GaAs MMIC Power Divider

MMIC Power divider

Model	Freq Range (GHz)	Insertion Loss (dB)	Insertion loss Flatness (dB)	VSWR	Isolation(dB)
GaPD0R35/2V	0.35-2	1	±0.2	1.6/1.3	13
GaPD0R5/1R5	0.5-1.5	0.9	±0.2	1.4/1.4	20
GaPD0R5/1R5V	0.5-1.5	0.8	±0.2	1.3/1.3	20
GaPD0R8/2	0.8-2.0	0.7	±0.1	1.5/1.4	12
GaPD1/3	1.0-3.0	0.8	±0.25	1.4/1.4	20
GaPD1/3V	1.0-3.0	0.8	±0.2	1.5/1.5	18
GaPD2/6	2.0-6.0	0.7	±0.2	1.5/1.3	17
GaPD2/6V	2.0-6.0	0.7	±0.2	1.3/1.2	20
GaPD2/8-2T	1-8	1.8	-	1.5/1.5	15
GaPD3/9	3.0-9.0	0.7	±0.2	1.4/1.3	20
GaPD3/9V	3.0-9.0	0.8	±0.2	1.4/1.3	20
GaPD2/18-2TA	2-18	1.0	±0.2	1.7/1.5	15
GaPD6/18	6-18	0.6	±0.15	1.5/1.3	17
GaPD6/18V	6-18	0.8	±0.4	1.3/1.4	20
GaPD8/12	8-12	0.4	±0.05	1.3/1.1	18
GaPD8/12V	8-12	0.5	±0.1	1.4/1.2	16
GaPD12/18	12-18	0.5	±0.2	1.4/1.1	20
GaPD18/26	18-26	0.6	±0.1	1.4/1.1	18
GaPD18/26V	18-26	0.7	±0.2	1.2/1.4	22
GaPD12/26R5	12-26.5	0.7	±0.2	1.4/1.5	20
GaPD20/40-3T	20-40	0.7	-	1.5/1.3	20
GaPD18/40	18-40	0.6	±0.1	1.4/1.4	11
GaPD18/40V	18-40	0.8	±0.2	1.2/1.1	25
GaPD26/31V	26-31	0.7	±0.2	1.3/1.2	24
GaPD26/40	26-40	0.5	±0.15	1.4/1.1	13

Performance charactisitc：

- Freq range： 0.35～2GHz
- insertion loss：1dB
- Insertion loss fluctuation：±0.2dB
- Isolation：13dB
- input/ouput VSWR：1.6/1.3
- Chip size：2.2mm×3.7mm×0.075mm

General Description：

This product is a GaAs MMIC 0 two-way power divider chip, which has the characteristics of small insertion loss, high isolation, small size and easy integration, and is widely used in power distribution and synthesis.Insertion throughout Freq Range is less than 1dB

Electrical Spec：（T_A=25℃，VD=+5V)

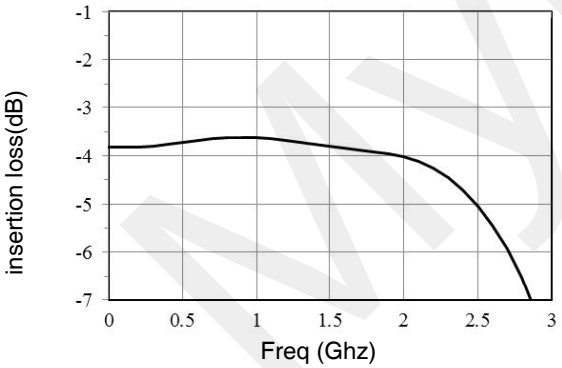
Items	Min	Typ	Max	Unit
Freq Range		0.35～2		GHz
insertion loss	0.7	1	1.1	dB
Insl Fluctucation			±0.2dB	dB
Isolation	13			dB
Input VSWR		1.6		dB
Output VSWR		1.3		dB

Absolute Max. Ratings：

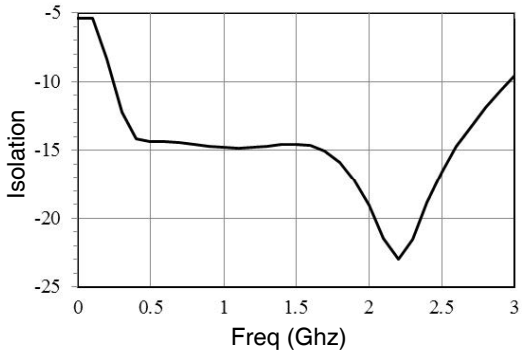
Max Input Power	+37dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

Typical curve：

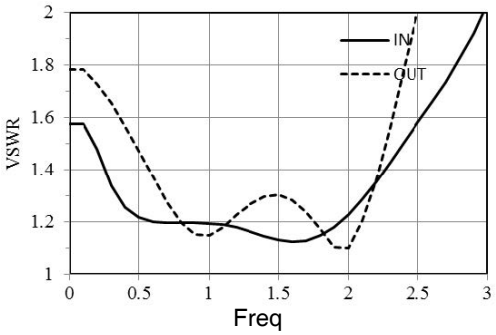
insertion loss



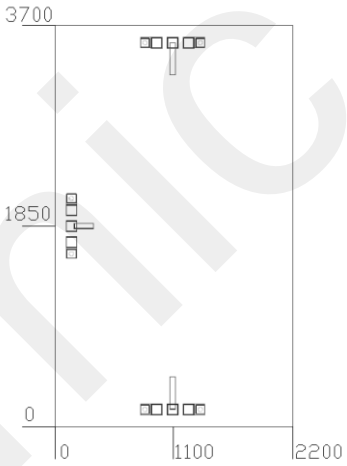
Isolation



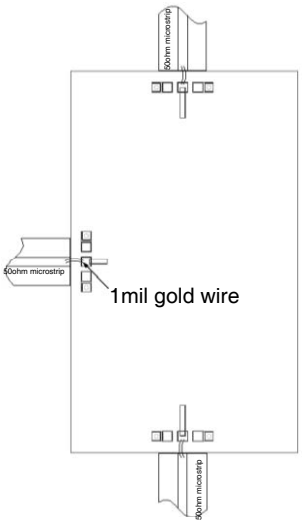
VSWR



Outline drawing：(Unit μm)



Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output with 2 Insertion throughout Freq Range(25um diameter gold wire) bonding wires, the bonding wire length is as short as possible;
- The input and output have a DC blocking capacitor. This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage.

Performance charactisitc：

- Freq Range：0.5～1.5 GHz
- Insertion Loss：0.9 dB
- Isolation：20dB
- Return Loss：＞17dB/＞17dB
- Chipsize1.5mm×1.3mm×0.1m
- interface：50Ω Coplanar waveguide line

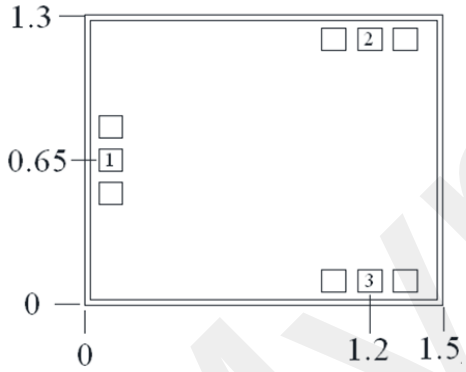
General Description：

This product is a gallium arsenide monolithic power divider chip.The power divider chip has the characteristics of small insertion loss, high isolation, small size, light weight, easy integration and the like, and is widely used in power distribution and synthesis.The chip adopts on-chip via metallization process to ensure good grounding. Metallization of the back surface is suitable for common use

Absolute Max. Ratings：

Max input Power	+30dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

Outline drawing：(Unit mm)



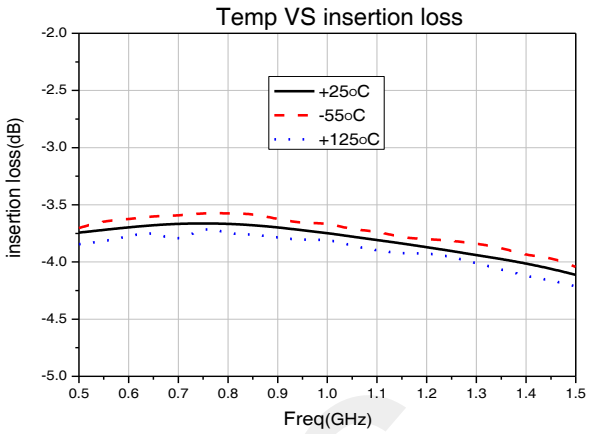
Descritpion：

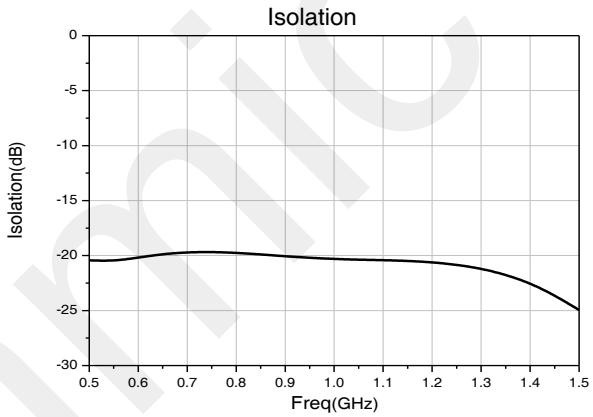
Description:
Unit: mm, tolerance: 0.05 mm
Gold plating and grounding on the back of the chip Bonding press point gold plating, press point size: 0.10mm*0.10mm Bonding cannot be performed on the through hole

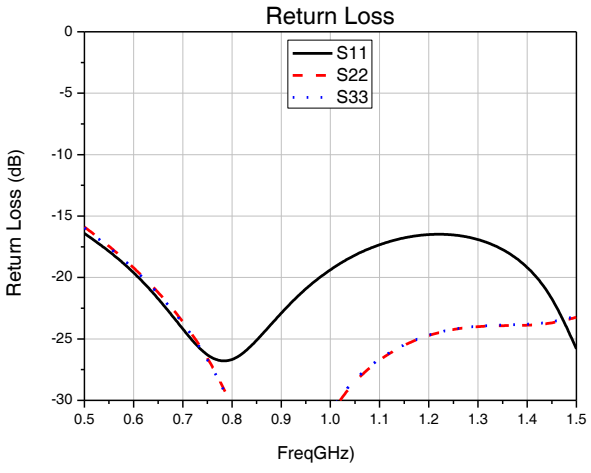
Pad Pad description：

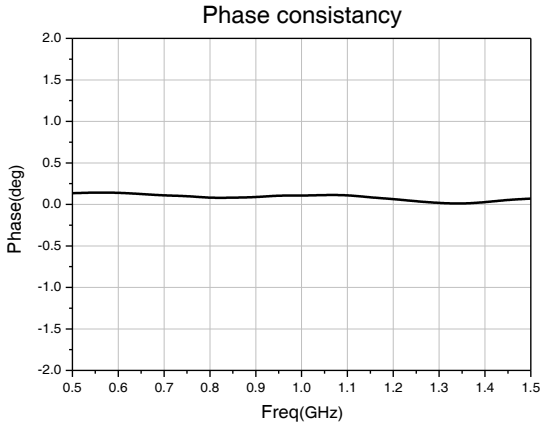
Pad number	Function	Fuction Description
1	RFin	RFInput，impedance) 50ohm
2、3	RFout	RF Output impedance 50ohm
	GND	

Typical curve：

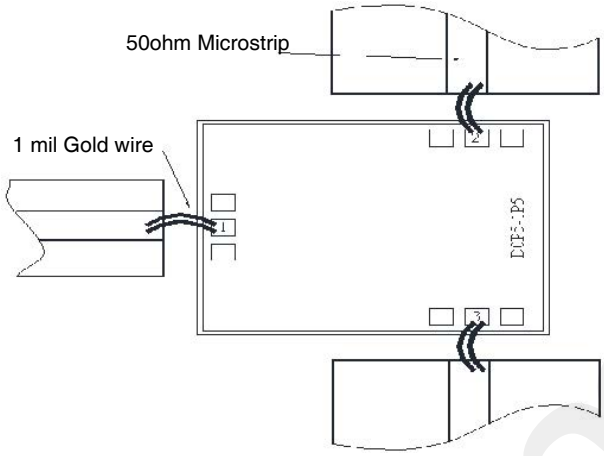








Assembly drawing：



The ceramic substrate should be as close to the chip as possible to shorten the size of the bond alloy wire.The typical assembly clearance is 0.076 - 0.152 mm (3 - 6 mils).

Instructions for assembly：

1. Storage: The chip must be placed in a container with electrostatic protection function and stored in a nitrogen atmosphere.
2. Cleaning: Bare chips must be operated and used in a clean environment. Cleaning the chips with liquid detergent is prohibited.
3. Electrostatic Protection: Please strictly observe ESD protection requirements to avoid electrostatic damage to the device.
4. General operation: Please use vacuum chuck or precision pointed tweezers to take the chip.Avoid touching the chip surface with tools or fingers during operation.
5. Mounting operation: AuSn solder eutectic sintering or conductive adhesive bonding can be used for chip mounting.The installation surface must be clean and level.
6. Bonding operation: ϕ 0.025 mm (1 mil) gold wire is used for both spherical and wedge bonding.
7. Thermoultrasonic bonding temperature is 150 C,Spherical bonding cleaver pressure 40 ~50gf, wedge bonding cleaver pressure 18 - 22gf.Use as little ultrasonic energy as possible. Bonding starts at the pressing point on the chip and ends at the package (or substrate)

Performance charactisitc：

- Freq range： 0.5～1.5GHz
- insertion loss：0.8dB
- Insertion loss fluctuation：±0.2dB
- Isolation：20dB
- input/ouput VSWR：1.3/1.3
- Chip size：1.5mm×1.3mm×0.075mm

General Description：

This product is a GaAs MMIC 0 two-way power divider chip. The power divider chip has the characteristics of small insertion loss, high isolation, small size, light weight and easy integration. The insertion loss in the whole FREQ Range is less than 1.0 dB.

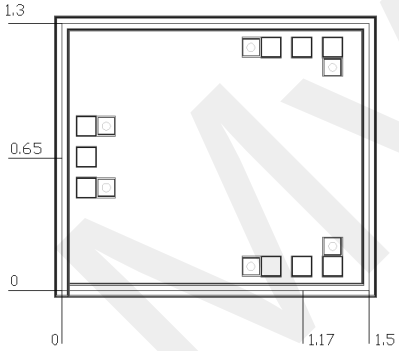
Electrical Spec：（T_A=25℃，VD=+5V）

Item	Min	Typ	Max	Unit
Freq Range	0.5～1.5			GHz
Insertion loss	0.6	0.8	1.0	dB
Insl Fluctuation		-	±0.2dB	dB
Isolation	19	20	25	dB
Input VSWR	1.1	1.3	1.5	-
Output VSWR	1.1	1.3	1.6	-

Absolute Max. Ratings：

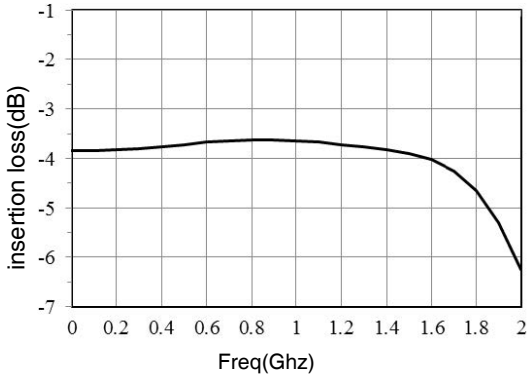
Max Input Power	+37dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

Outline drawing：（Unit mm）

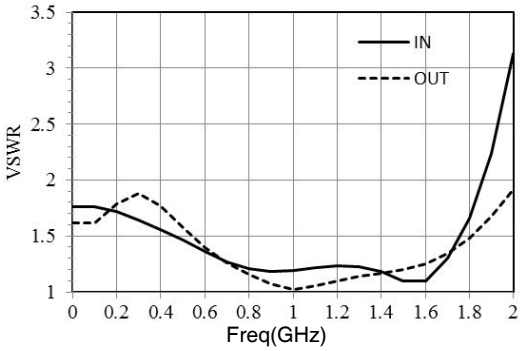


Typical curve：

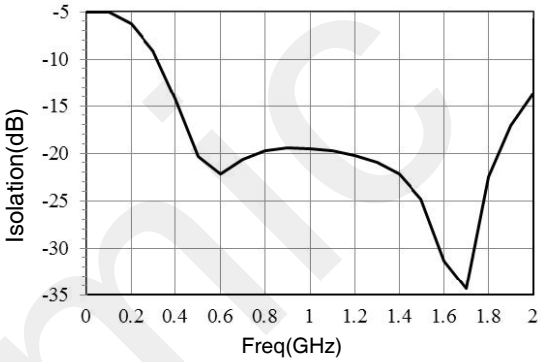
insertion loss



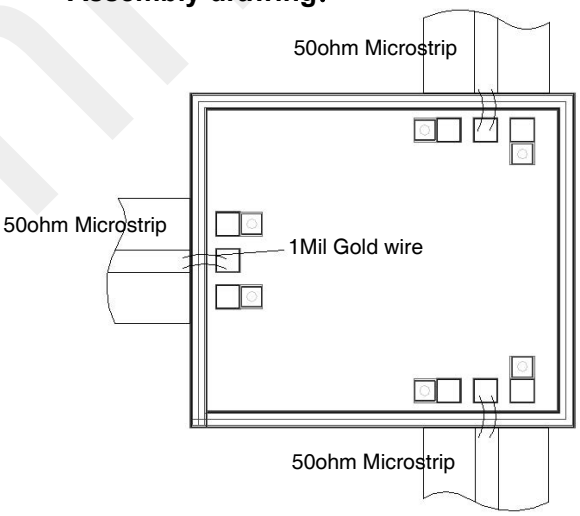
In/Output VSWR



Isolation



Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output with 2 (25um diameter gold wire) bonding wires, the bonding wire length is as short as possible;
- The input and output have a DC blocking capacitor.
- This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage.

Performance charactisitc：

- Freq range：0.8～2GHz
- insertion loss：0.7dB
- Insertion loss fluctuation：±0.1dB
- input/ouput VSWR：1.5/1.4
- Chip size：2.2mm×1.5mm×0.1mm

General Description：

This product is a GaAs MMIC 0 two-way power divider with excellent performance.The chip does not need to be powered on, its freq range covers 0.8 - 2.0 GHz, insertion loss is less than 0.8 db, and input and output voltages

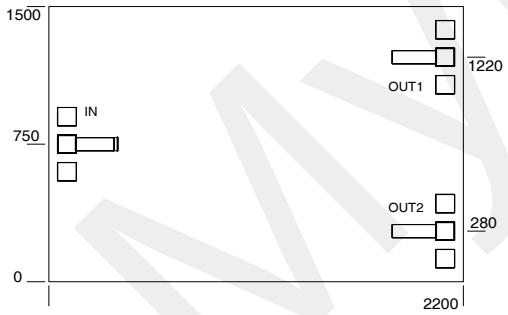
Electrical Spec：（T_A=25℃，VD=+5V)

	Min	Typ	Max	Unit
Freq Range		0.8-2		GHz
Insertion loss	0.6	0.7	0.8	dB
Insl Fluctuation			±0.1	dB
Isolation	12			dB
Input VSWR			1.5	-
Output VSWR			1.4	-

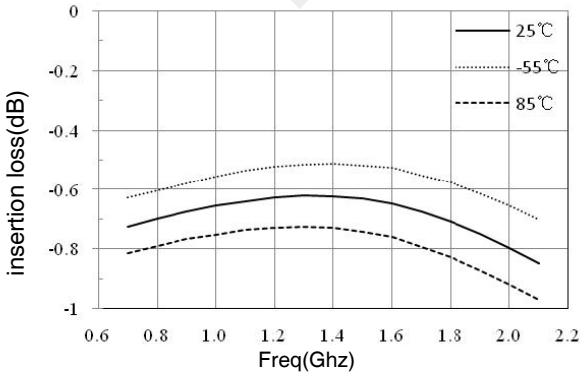
Absolute Max. Ratings：

Max input Power	+37 dBm
Storage temp	-65℃-150℃
Operation Temp	-55℃-125℃

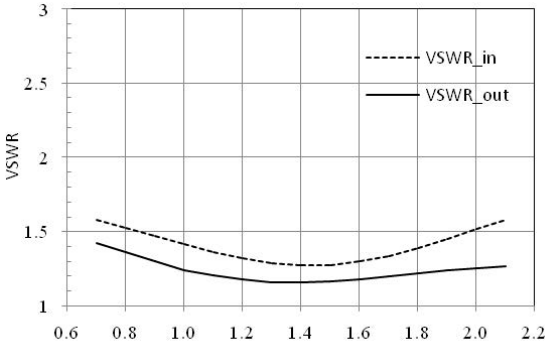
Outline drawing：（Unitμm）



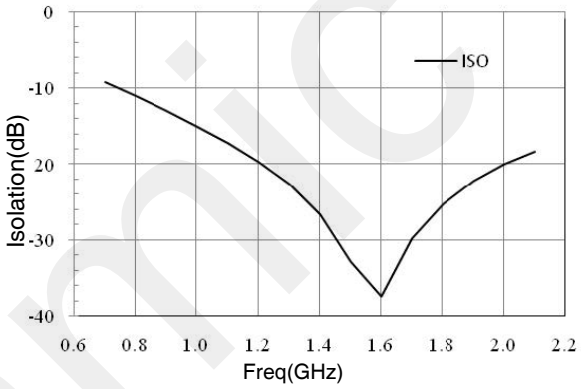
insertion loss



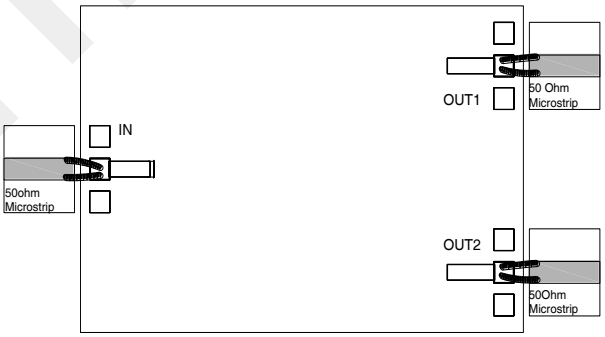
In/Output VSWR



Isolation



Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output with 2 (25um diameter gold wire) bonding wires, the bonding wire length is as short as possible;
- The input and output have a DC blocking capacitor.
- This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage

Performance charactisitc：

- Freq Range：1.0～3.0 GHz
- Insertion Loss：0.8 dB
- Isolation：20dB
- Return Loss：＞16dB/＞17dB
- Chip size：1.5mm×1.2mm×0.1mm
- interface：50Ω Coplanar wave guide-line

General Description

This product is a gallium arsenide monolithic power divider chip. The power divider chip has the characteristics of small insertion loss, high isolation, small size, light weight, easy integration and the like, and is widely used in power distribution and synthesis. The chip adopts on-chip via metallization process to ensure good grounding. Metallization of the back surface is suitable for eutectic sintering and conductive adhesive bonding.

Absolute Max. Ratings：

Max Input Power	+30dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

Outline drawing：（Unitmm）

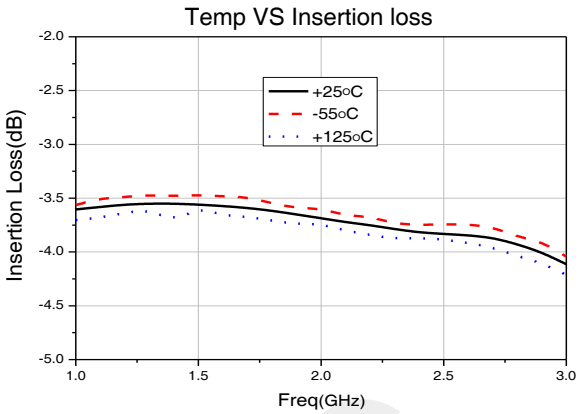
Description:

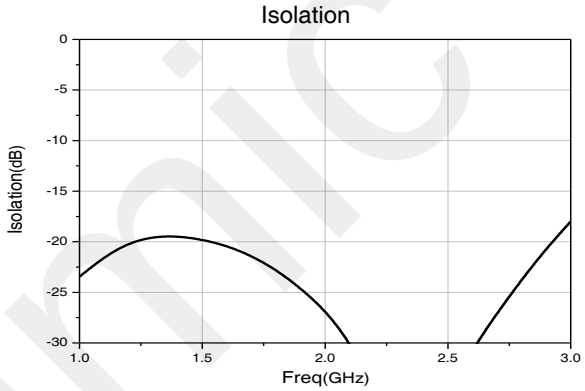
Unit: mm, tolerance: 0.05 mm
Gold plating and grounding on the back of the chip
Bonding press point gold plating, press point size: 0.10mm*0.10mm
Bonding cannot be performed on the through hole

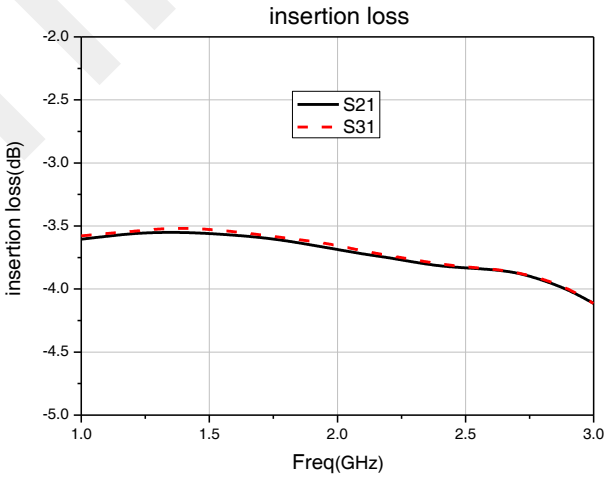
Pad description：

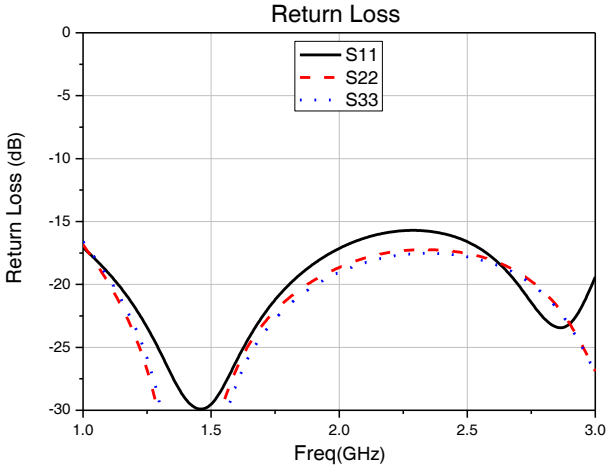
Pad number	Function	Fuction Description
1	RFin	RFInput，impedance) 50ohm
2、3	RFout	RF Output impedance 50ohm
	GND	

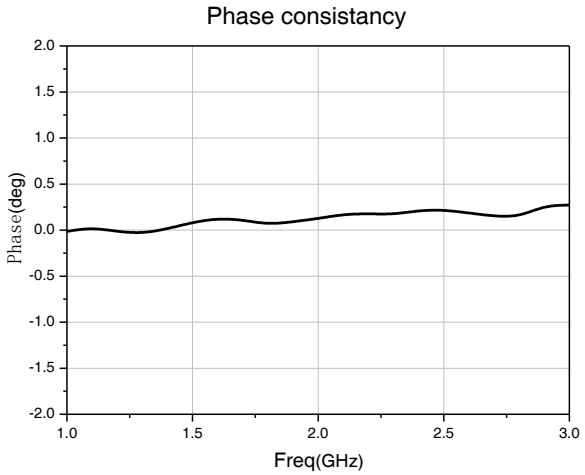
Typical curve：



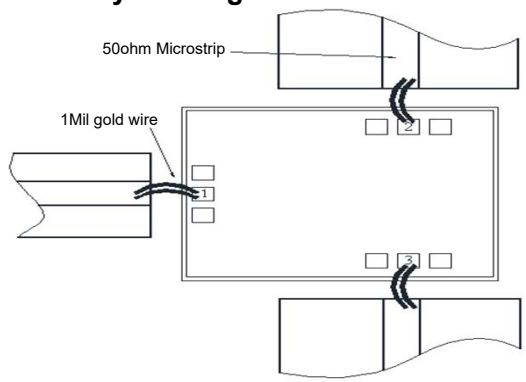








Assembly drawing：



The ceramic substrate should be as close to the chip as possible to shorten the size of the bond alloy wire.
The typical assembly clearance is 0.076 - 0.152 mm (3 - 6 mils).

Instructions for assembly：

1. Storage: The chip must be placed in a container with electrostatic protection function and stored in a nitrogen atmosphere.
2. Cleaning: Bare chips must be operated and used in a clean environment. Cleaning the chips with liquid detergent is prohibited.
3. Electrostatic Protection: Please strictly observe ESD protection requirements to avoid electrostatic damage to the device.
4. General operation: Please use vacuum chuck or precision pointed tweezers to take the chip.
   Avoid touching the chip surface with tools or fingers during operation.
5. Mounting operation: AuSn solder eutectic sintering or conductive adhesive bonding can be used for chip mounting.The installation surface must be clean and level.
6. Bonding operation: Φ 0.025 mm (1 mil) gold wire is used for both spherical and wedge bonding.
7. Thermoultrasonic bonding temperature is 150 C,Spherical bonding cleaver pressure 40 ~50gf, wedge bonding cleaver pressure 18 - 22gf.Use as little ultrasonic energy as possible. Bonding starts at the pressing point on the chip and ends at the package (or substrate)

Performance charactisitc：

- Freq range：1.0～3.0 GHz
- insertion loss：0.8 dB
- Insertion loss fluctuation：±0.2dB
- Isolation:18dB
- input/ouput: VSWR：1.5/1.5
- Chip size：1.5mm×1.2mm×0.075mm

General Description：

ThisproductisaGaAsMMIC0two-waypower divider chip,whichhasthecharacteristicsof smallinsertion loss,highisolation,smallsize andeasyintegration, andis widelyusedinpower distributionand synthesis.Thefreqrangecovers 1-3GHz,andthe insertionlosswithin the entirefreqrangeisless than 0.8db.

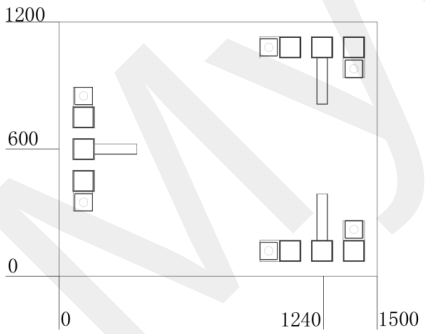
Electrical Spec：(TA=25℃，VD=+5V)

Item	Min	Typ	Max	Unit
Freq Range		1-3		GHz
insertion loss	0.6	0.8	1	dB
InselFluctuate			±0.2	dB
Isolation	18			dB
Input VSWR		1.5		-
Output VSWR		1.5		-

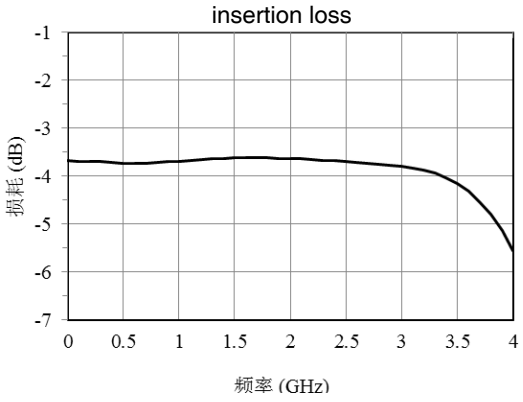
Absolute Max. Ratings：

Max Input Power	+37dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

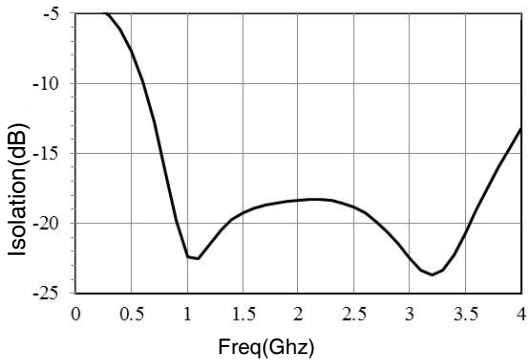
Outline drawing：（Unitμm）



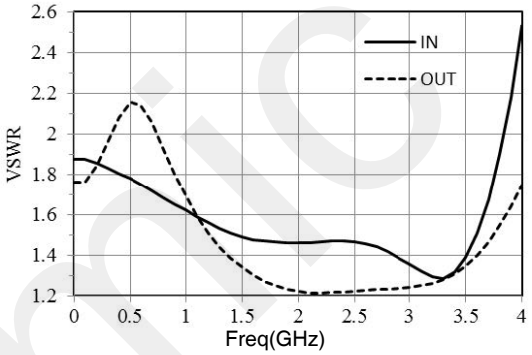
Typical curve：



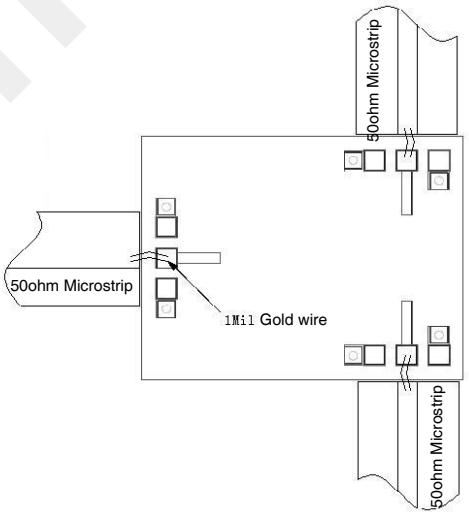
Isolation



VSWR



Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output with 2 (25um diameter gold wire) bonding wires, the bonding wire length is as short as possible;
- The input and output have a DC blocking capacitor.
- This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage

Performance charactisitc：

- Freq range： 2～6GHz
- insertion loss：0.7dB
- Insertion loss fluctuation：±0.2dB
- input/ouput VSWR：1.5/1.3
- Chip size：1.5mm×1.65mm×0.1mm

General Description：

This product is a GaAs MMIC 0 two-way power divider chip,its FREQ Range covers 2 ～6 GHz,and the insertion loss is less than 0.9 dB in the entire Freq Range.

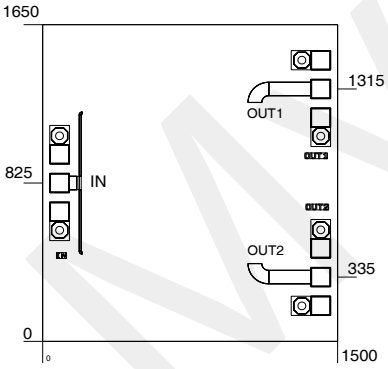
Electrical Spec：(TA=25℃，VD=+5V)

Items	Min	Typ	Max	Unit
Freq Range		2～6		GHz
Insertion loss	0.5	0.7	0.9	dB
INSL Fluctuation			±0.2dB	dB
Isolation	17			dB
Input VSWR		1.5		-
Output VSWR		1.3		-

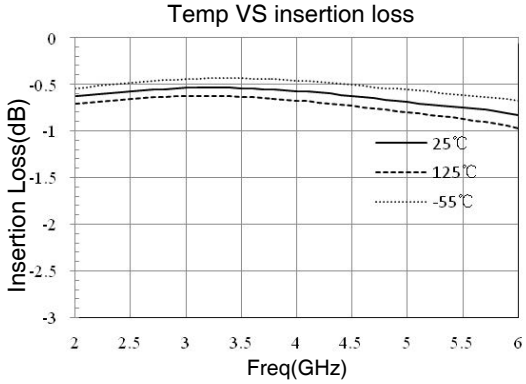
Absolute Max. Ratings：

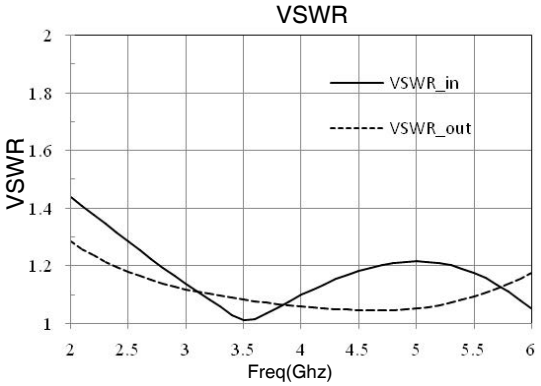
Max Input Power	+37dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

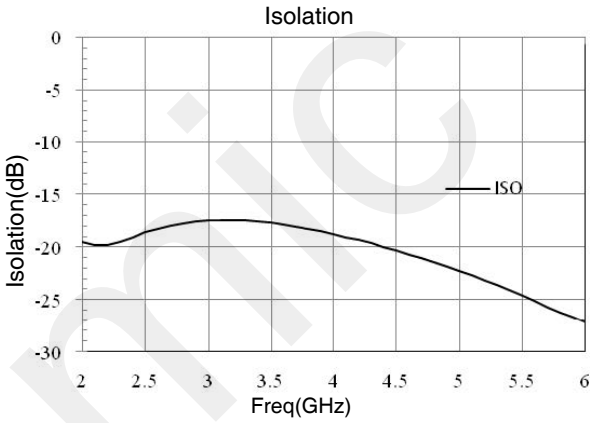
Outline drawing：（Unitμm）



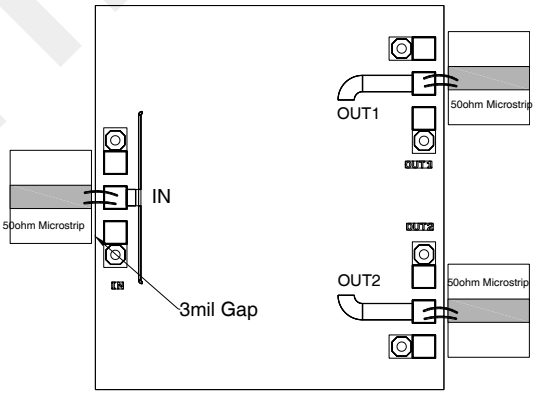
Typical curve：







Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output with 2 (25um diameter gold wire) bonding wires, the bonding wire length is as short as possible;
- The input and output have a DC blocking capacitor.
- This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage

Performance charactisitc：

- Freq range： 2～6GHz
- insertion loss：0.7dB
- Insertion loss fluctuation：±0.2dB
- Isolation：20dB
- input/ouput VSWR：1.3/1.2
- Chip size：1.2mm×1.0mm×0.075mm

General Description：

This product is a GaAs MMIC 0 two-way power divider chip, which has the characteristics of small insertion loss, high isolation, small size and easy integration, and is widely used in power distribution and synthesis.

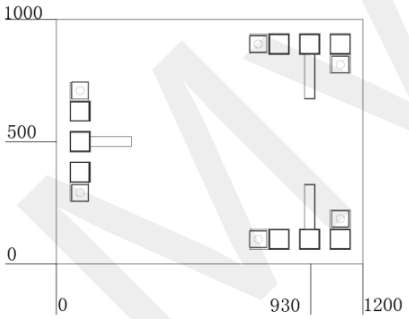
Electrical Spec：（T_A=25℃，VD=+5V)

Item	Min	Typ	Max	Unit
Freq Range		2～6		GHz
Insertion loss	0.5	0.7	0.9	dB
INSL Fluctuation			±0.2	dB
Isolation	18	20		dB
Input VSWR		1.3		-
Output VSWR		1.2		-

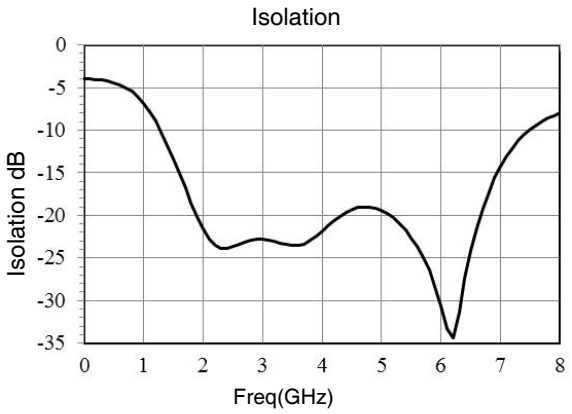
Absolute Max. Ratings：

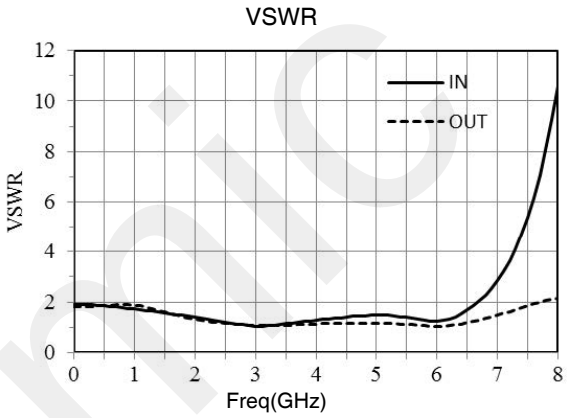
Max Input Power	+37dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

Outline drawing：（Unitμm）

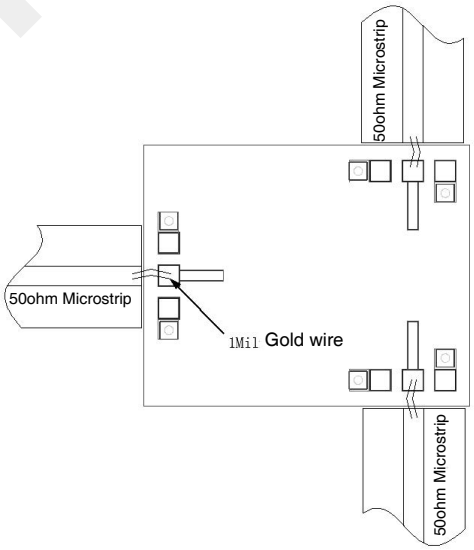


Typical curve：





Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output with 2 (25um diameter gold wire) bonding wires, the bonding wire length is as short as possible;
- The input and output have a DC blocking capacitor.
- This product is an electrostatic sensitivedevice. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage

Performance charactisitc：

- Freq Range：1～8 GHz
- Insertion Loss：1.8 dB
- Isolation：15dB
- Return Loss：15dB
- Chip size：1.4mm×0.9mm×0.1mm
- interface：50Ω Coplanar waveguide line

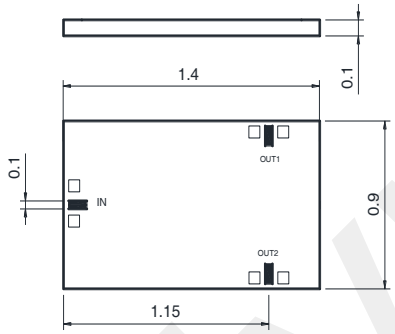
General Description：

This product is a GaAs monolithic power divider chip. The power divider chip has the characteristics of small insertion loss, high isolation, small size, light weight, easy integration and the like, and is widely used in power distribution and synthesis.
The chip adopts on-chip via metallization process to ensure good grounding. Metallization of the back surface is suitable for eutectic sintering and conductive adhesive bonding.

Absolute Max. Ratings：

Max Input Power	+30dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃ ～+125℃

Outline drawing：（Unitmm）

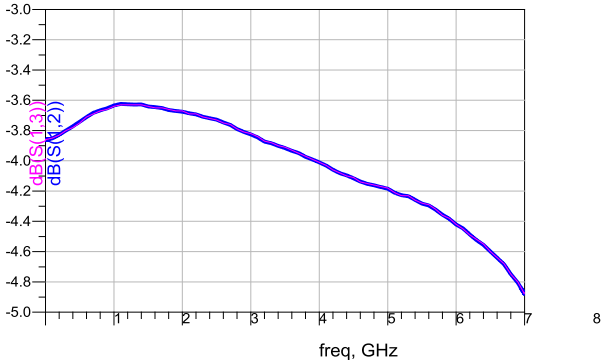


Description：

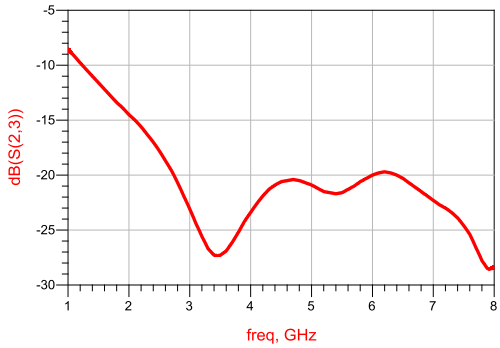
Gold plating and grounding on the back of the chip
Bonding press point gold plating, press point size:
0.10mm*0.10mm
Bonding cannot be performed on the through hole

Typical curve：

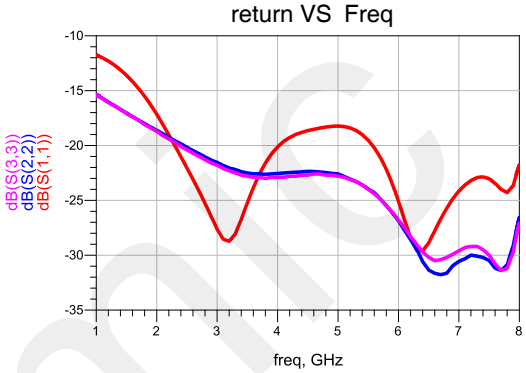
Insertion loss(Split Loss inclusive)VS Freq



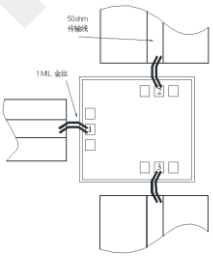
Isolation VS Freq



return VS Freq



Assembly drawing：



The ceramic substrate should be as close to the chip as possible to shorten the size of the bond alloy wire. The typical assembly clearance is 0.076 - 0.152 mm (3 - 6 mils).

Instructions for assembly:

1. Storage: The chip must be placed in a container with electrostatic protection function and stored in a nitrogen atmosphere.
2. Cleaning: Bare chips must be operated and used in a clean environment. Cleaning the chips with liquid detergent is prohibited.
3. Electrostatic Protection: Please strictly observe ESD protection requirements to avoid electrostatic damage to the device.
4. General operation: Please use vacuum chuck or precision pointed tweezers to take the chip.avoid touching the chip surface with tools or fingers during operation.
5. Mounting operation: AuSn solder eutectic sintering or conductive adhesive bonding can be used for chip mounting.The installation surface must be clean and level.
6. Bonding operation: ϕ 0.025 mm (1 mil) gold wire is used for both spherical and wedge bonding.
7. Thermo ultrasonic bonding temperature is 150 C,Spherical bonding cleaver pressure 40 ~50gf, wedge bonding cleaver pressure 18 -22gf.Use as little ultrasonic energy as possible. Bonding starts at the pressing point on the chip and ends at the package (or substrate)

Performance charactisitc：

- Freq Range：3～9 GHz
- Insertion Loss：0.7 dB
- Isolation：20dB
- Return：＞16dB/＞18dB
- Chip size：1.2mm×1.0mm×0.1mm
- interface：50Ω Coplanar waveguide line

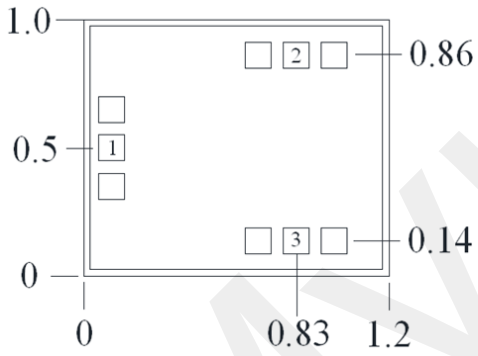
General Description：

This product is a gallium arsenide monolithic power divider chip.The power divider chip has the characteristics of small insertion loss, high isolation,small size, light weight, easy integration and the like, and is widely used in power distribution and synthesis. The chip adopts on-chip via metallization process to ensure good grounding. Metallization of the back surface is suitable for common use

Absolute Max. Ratings：

Max Input Power	+30dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

Outline drawing：（Unitmm）



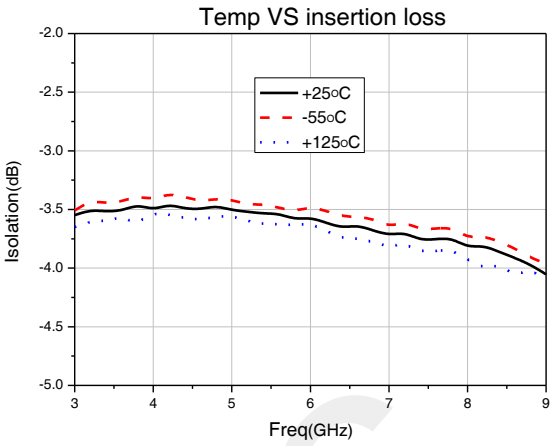
Description:

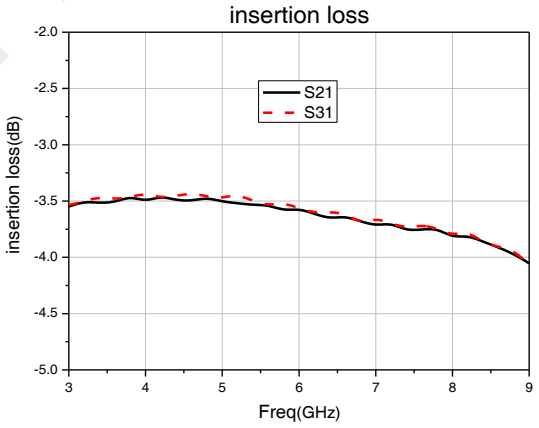
Unit: mm, tolerance: 0.05 mm Gold plating and grounding on the back of the chip Bonding press point gold plating, press point size: 0.10mm*0.10mm
Bonding cannot be performed on the through hole

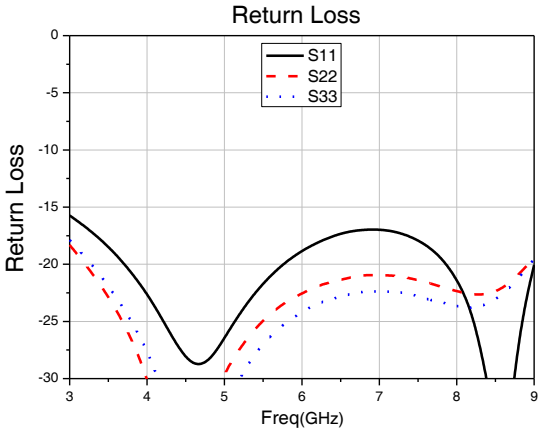
Pad description：

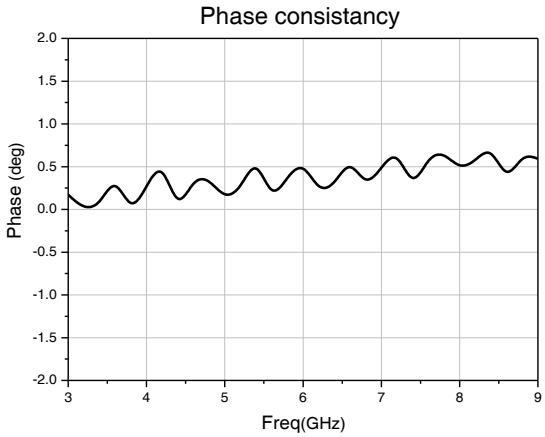
Pad number	Function	Fuction Description
1	RFin	RFInput，impedance) 50ohm
2、3	RFout	RF Output impedance 50ohm
	GND	

Typical curve：

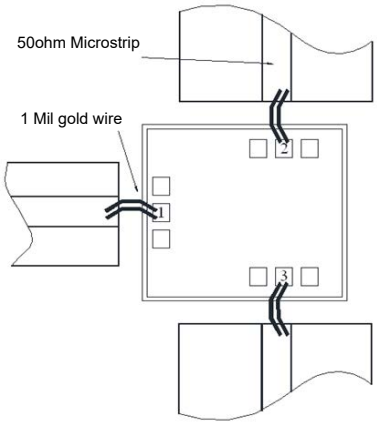








Assembly drawing:



The ceramic substrate should be as close to the chip as possible to shorten the size of the bond alloy wire.
The typical assembly clearance is 0.076 - 0.152 mm (3 - 6 mils).

Instructions for assembly:

1. Storage: The chip must be placed in a container with electrostatic protection function and stored in a nitrogen atmosphere.
2. Cleaning: Bare chips must be operated and used in a clean environment. Cleaning the chips with liquid detergent is prohibited.
3. Electrostatic Protection: Please strictly observe ESD protection requirements to avoid electrostatic damage to the device.
4. General operation: Please use vacuum chuck or precision pointed tweezers to take the chip. Avoid touching the chip surface with tools or fingers during operation.
5. Mounting operation: AuSn solder eutectic sintering or conductive adhesive bonding can be used for chip mounting. The installation surface must be clean and level.
6. Bonding operation: ϕ 0.025 mm (1 mil) gold wire is used for both spherical and wedge bonding.
7. Thermoultrasonic bonding temperature is 150 C,Spherical bonding cleaver pressure 40 ~50gf, wedge bonding cleaver pressure 18 - 22gf.Use as little ultrasonic energy as possible. Bonding starts at the pressing point on the chip and ends at the package (or substrate)

Performance charactisitc：

- Freq Range：3～9 GHz
- Insertion Loss：0.8 dB
- Insertion loss fluctuation：±0.2dB
- Isolation：20dB
- input/ouput VSWR：1.4/1.3
- Chip size：1.2mm×1.0mm×0.075mm

General Description：

This product is a GaAs MMIC 0 two-way power divider chip, which has the characteristics of small insertion loss, high isolation, small size and easy integration, and is widely used in power distribution and synthesis.The freq range covers 3 - 9 GHz, and the insertion loss within the entire freq range is less than 0.9 db.

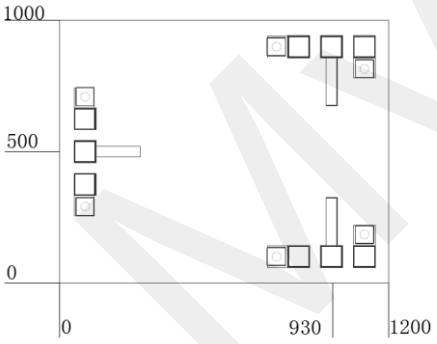
Electrical Spec：(TA=25℃)

Item	Min	Typ	Max	Unit
Freq Range	3～9			GHz
insertion loss	0.5	0.7	0.9	dB
Insertion loss fluctuation			±0.2	dB
Isolation	-	20	-	dB
Input VSWR	1.5	1.4	-	-
Output VSWR	1.4	1.3	-	-

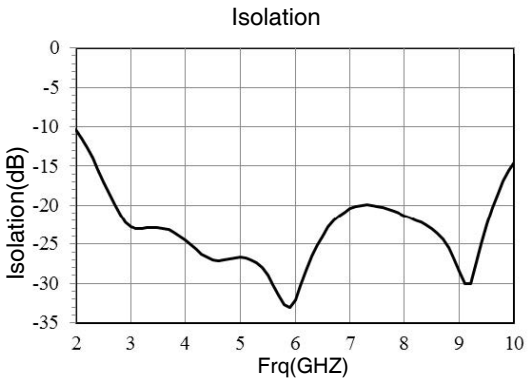
Absolute Max. Ratings：

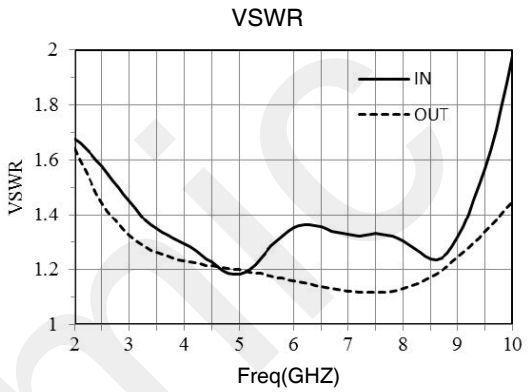
Max Input Power	+37dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

Outline drawing：（Unitμm）

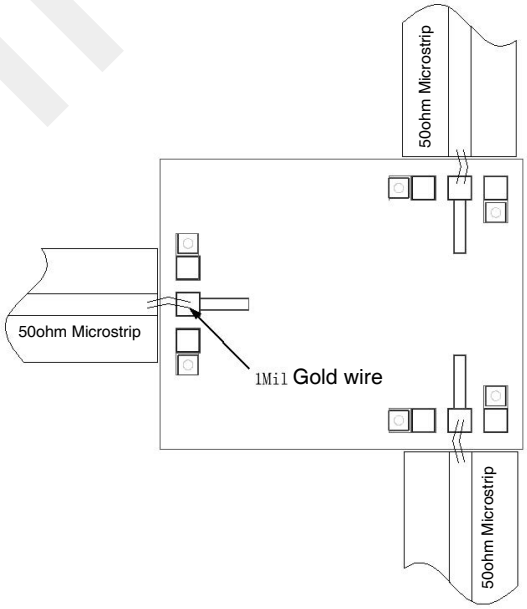


Typical curve：





Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output with 2 (25um diameter gold wire) bonding wires, the bonding wire length is as short as possible;
- The input and output have a DC blocking capacitor.
- This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage

Performance charactisitc：

- Freq range： 2～18GHz
- insertion loss：1dB
- Isolation：15dB
- Input/Output return Loss：15dB
- Chip size： 2.0×2.0×0.1mm

General Description：

This product is a GaAs MMIC 0 two-way power divider chip，FreqRangeCover2～18GHz。

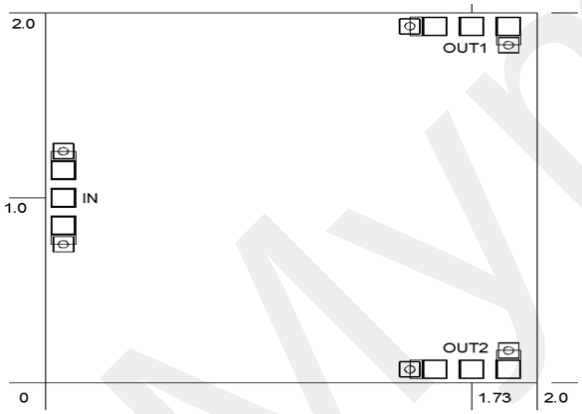
Electrical Spec：（T_A=25℃）

Item	Min	Typ	Max	Unit
Freq Range	2～18			GHz
insertion loss	0.5	0.8	1.4	dB
Isolation	-	17	-	dB
Return Loss	-	15	-	dB
Output VSWR		15		-

Absolute Max. Ratings：

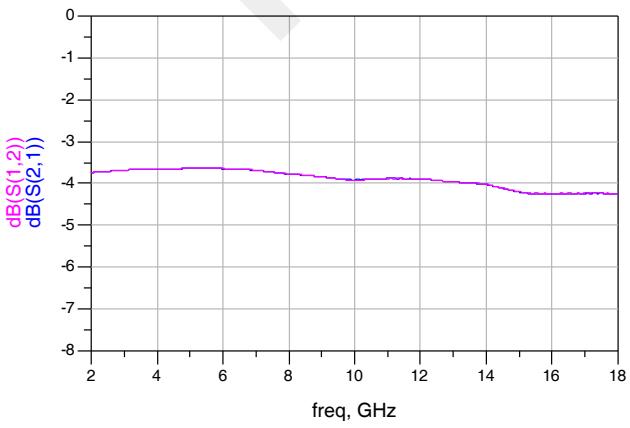
Max Input Power	+37dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

Outline drawing：（Unitmm）

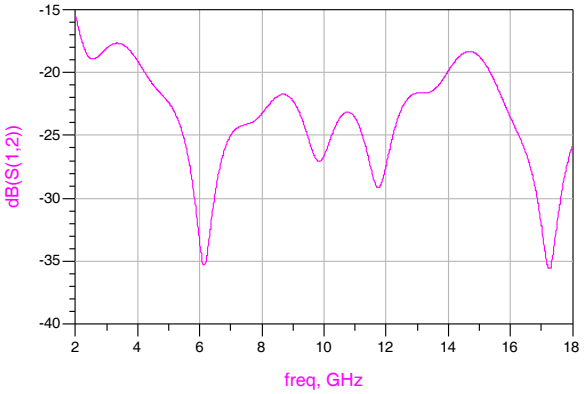


Typical curve：

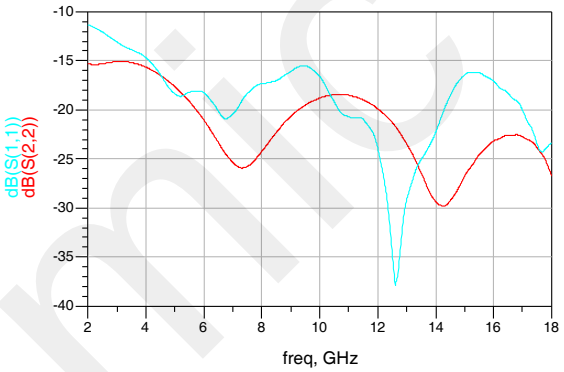
insertion loss



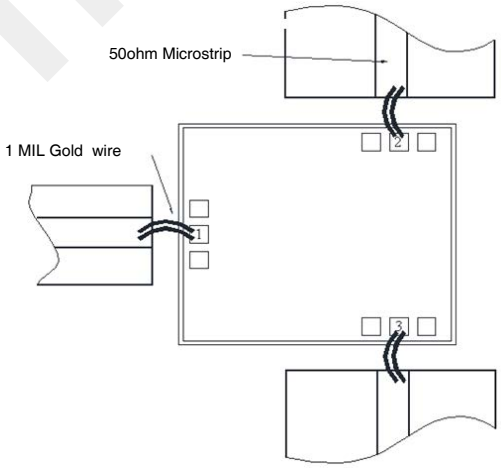
Isolation



VSWR



Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output with 2 (25um diameter gold wire) bonding wires, the bonding wire length is as short as possible;
- The input and output have a DC blocking capacitor.

Performance charactisitc：

- Freq Range：6～18GHz
- insertion loss：0.6dB
- input/ouput VSWR：1.5/1.3
- Chip size：1.5mm×2.1mm×0.1mm

General Description：

This product is a GaAs MMIC 0 two-way power divider chip，he chip is grounded through the back metal via the through hole，Freqrange Cover6-18 GHz，insertionloss isLessthan0.6dB，Input/ Output VSWR is less than 1.5。

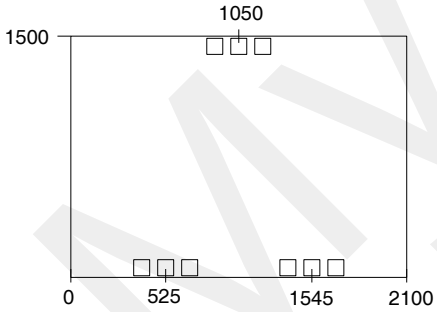
Electrical Spec：(TA=25℃)

Items	Min	Typ	Max	Unit
Freq Range	6-18			GHz
insertion loss	0.3		0.6	dB
Insertion loss fluctuation			±0.15	dB
Isolation	17			dB
Input VSWR			1.5	-
Output VSWR			1.3	-

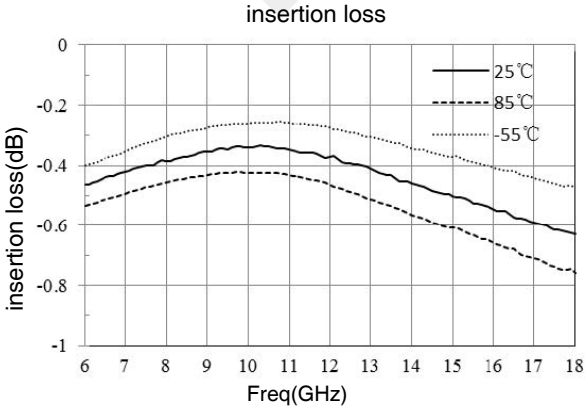
Absolute Max. Ratings：

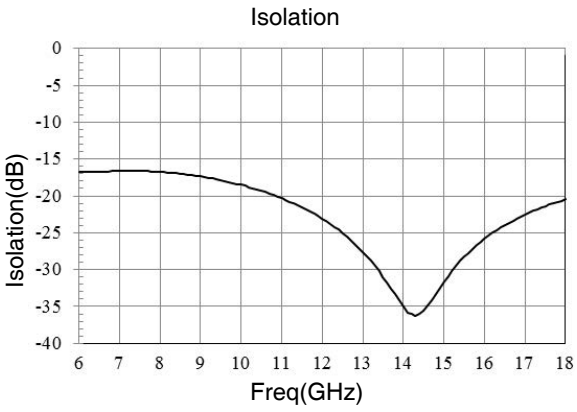
Max input Power	37dBm
Storage temp	-65℃-+150℃
Operation Temp	-55℃-+125℃

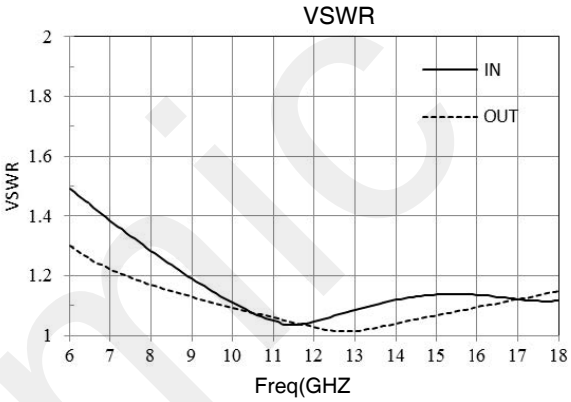
Outline drawing：（Unitμm）



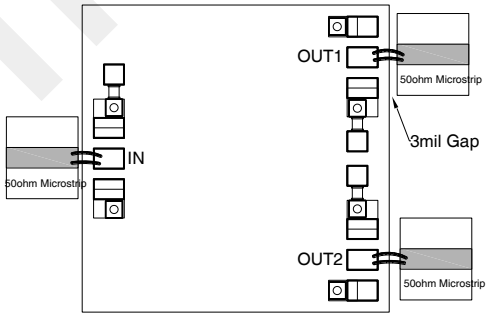
Typical curve：







Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output are made of two (25um diameter gold wire) bonding wires, with a bonding wire length of about 300 um being optimal.
- Input and output have no direct isolation capacitance;
- This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage.

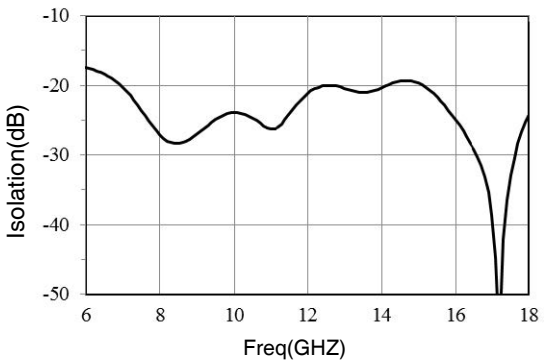
Performance charactisitc：

- Freq Range：6～18GHz
- insertion loss：0.8dB
- Insertion loss fluctuation：±0.4dB
- Isolation：20dB
- input/ouput VSWR：1.3/1.4
- Chip size：1.5mm×1.5mm×0.075mm

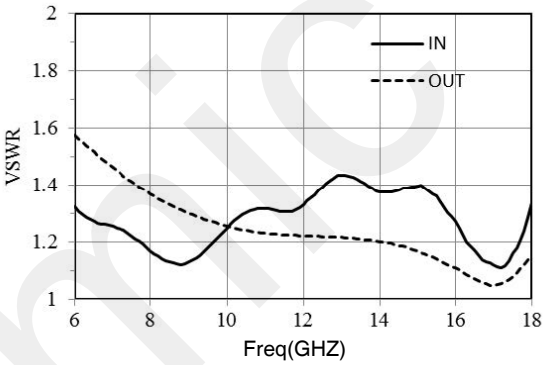
General Description：

This product is a GaAs MMIC 0 degree two-way power divider with excellent performance. The chip is grounded through the back metal via the through hole. The chip Freq Range covers 6 - 18 GHz, the insertion loss is less than 0.6 dB, and the input and output voltage VSWR is less than 1.5

Isolation



VSWR



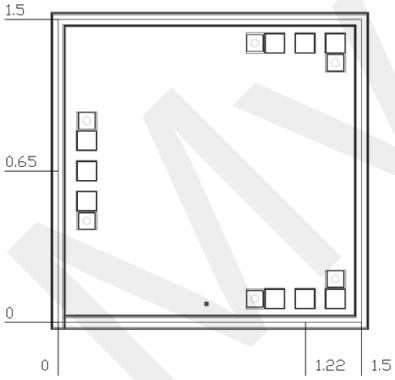
Electrical Spec：(TA=25℃，VD=+5V)

Item	Min	Typ	Max	Unit
Freq Range		6-18		GHz
insertion loss	0.4	0.8	1.2	dB
INSL Fluctuation			±0.4	dB
Isolation	17	20	57	dB
Input VSWR	1.1	1.3	1.5	-
Output VSWR	1.1	1.4	1.6	-

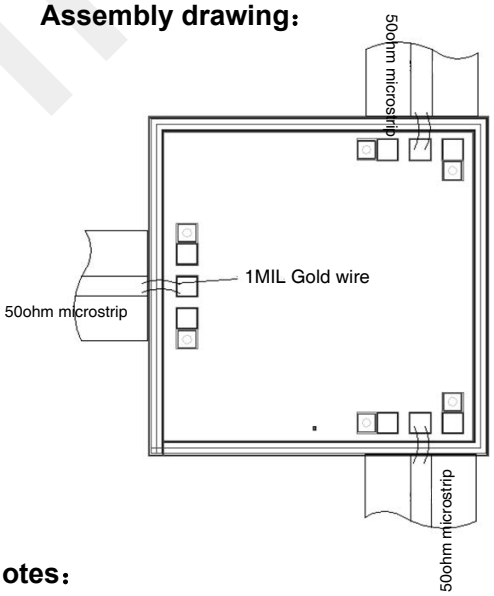
Absolute Max. Ratings：

Max input Power	+37dBm
Storage temp	-65℃-+150℃
Operation Temp	-55℃-+125℃

Outline drawing：（Unitmm）

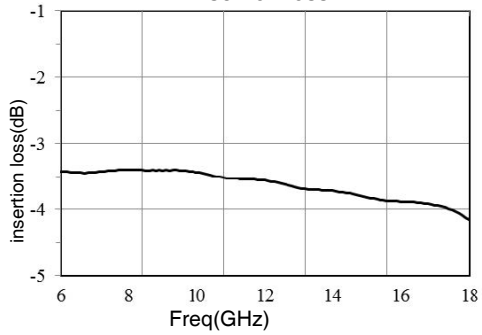


Assembly drawing：



Typical curve：

insertion loss



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output are made of two (25um diameter gold wire) bonding wires, with a bonding wire length of about 300 um being optimal.
- Input and output have no direct isolation capacitance;
- This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage.

Performance charactisitc：

- Freq Range：8～12GHz
- insertion loss：0.4dB
- input/ouput VSWR：1.3/1.1
- Chip size：1.5mm×4.0mm×0.1mm

General Description：

This product is a GaAs MMIC 0 degree two-way power divider with excellent performance. The chip freq range covers 8-12 GHz, the insertion loss is less than 0.4 db, and the input and output voltage VSWR is less than 1.3.

Electrical Spec：（TA=25℃）

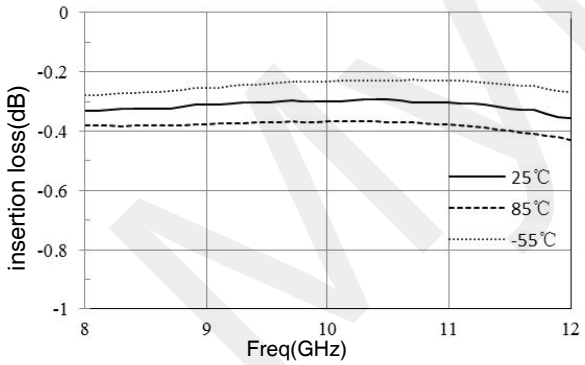
Item	Min	Typ	Max	Unit
Freq Range	8-12			GHz
insertion loss	0.3		0.4	dB
INSLFluctuation			±0.05	dB
Isolation	18			dB
Input VSWR			1.3	-
Output VSWR			1.1	-

Absolute Max. Ratings：

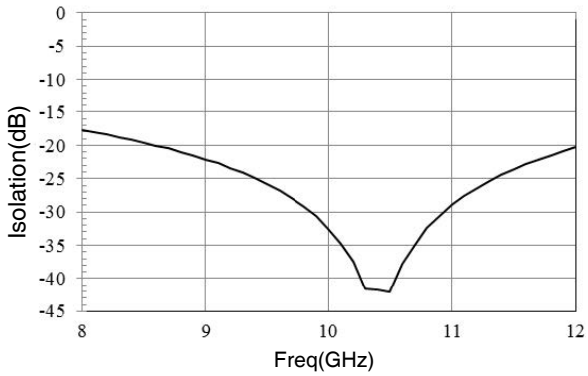
Max input Power	+37dBm
Storage temp	-65℃-+150℃
Operation Temp	-55℃-+125℃

Typical curve：

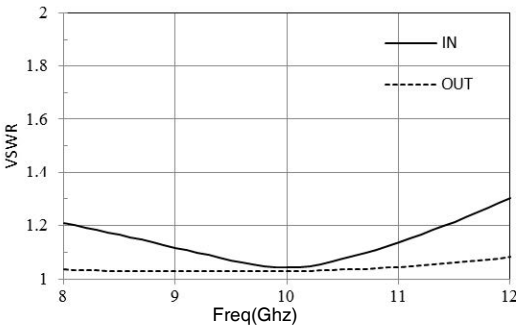
insertion loss



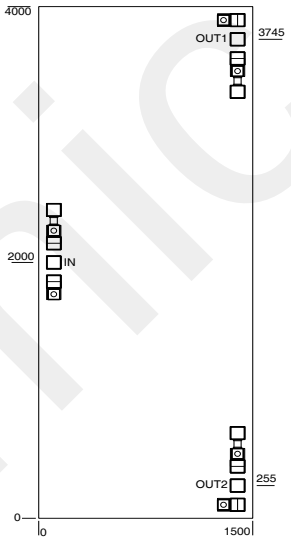
Isolation



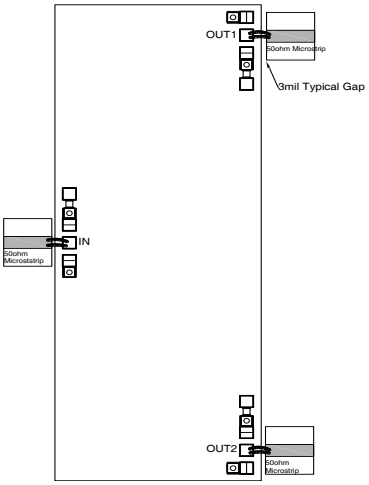
VSWR



Outline drawing：（Unitμm）



Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output are made of two (25um diameter gold wire) bonding wires, with a bonding wire
- length of about 300 um being optimal.
  Input and output have no direct isolation capacitance;
- This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage.

Performance charactisitc：

- Freq Range：8～12GHz
- insertion loss：0.5dB
- input/ouput VSWR：1.4/1.2
- Chip size：1.1mm×1.5mm×0.075mm

General Description：

This product is a GaAs MMIC 0 two-way power divider with excellent performance.The chip freq range covers 8 - 12 GHz and the insertion loss is less than 0.5DB, input and output voltage VSWR is less than 1.4.

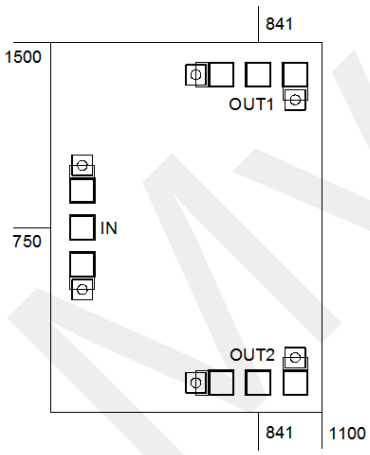
Electrical Spec：（TA=25℃，VD=+5V)

Item	Min	Typ	Max	Unit
Freq Range	8-12			GHz
insertion loss	0.3		0.5	dB
INSL Fluctuation			±0.1	dB
Isolation	16			dB
Input VSWR			1.4	-
Output VSWR			1.2	-

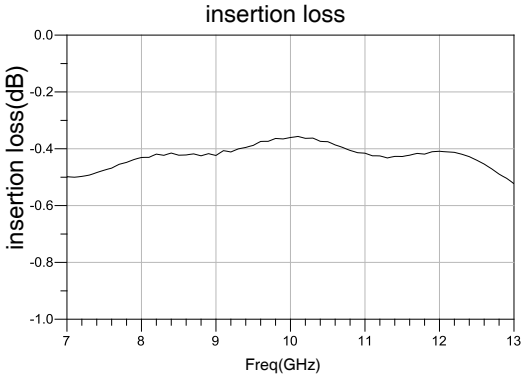
Absolute Max. Ratings：

Max input Power	+37dBm
Storage temp	-65℃-+150℃
Operation Temp	-55℃-+125℃

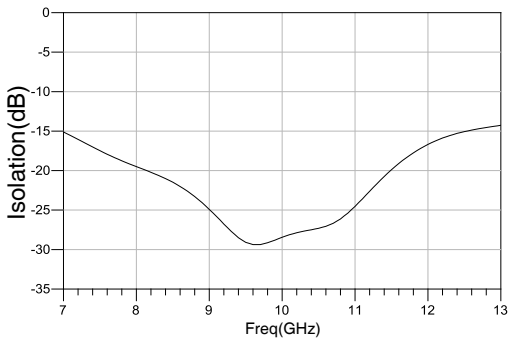
Outline drawing：（Unitμm）



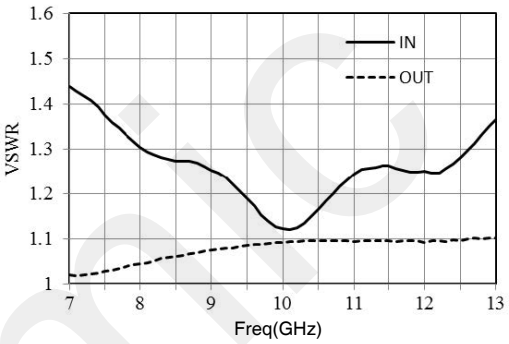
Typical curve：



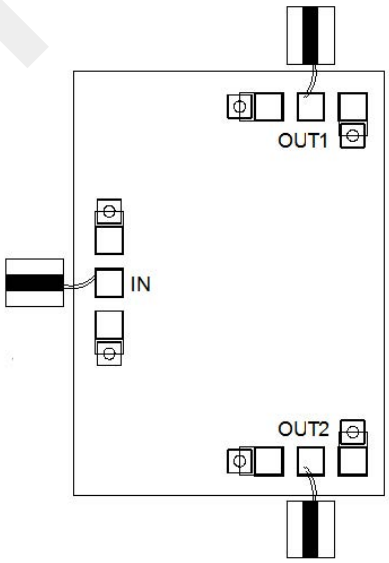
Isolation



VSWR



Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output are made of two (25um diameter gold wire) bonding wires, with a bonding wire length of about 300 um being optimal.
- This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage.

Performance charactisitc：

- Freq Range：12～18 GHz
- Insertion Loss：0.5 dB
- Isolation：20dB
- Return Loss：＞18dB/＞26dB
- Chip size：1.5mm×1.5mm×0.1mm
- interface：50Ω Coplanar waveguide line

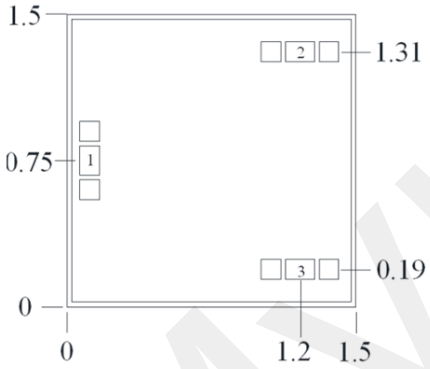
General Description：

The power divider chip has the characteristics of small insertion loss, high isolation, small volume, light weight, easy integration and the like Point, widely used in power distribution and synthesis. The chip adopts on-chip via metallization process to ensure good grounding. Metallization of the back surface is suitable for eutectic sintering and conductive adhesive bonding.

Absolute Max. Ratings：

Max input Power	+30dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

Outline drawing：（Unitmm）



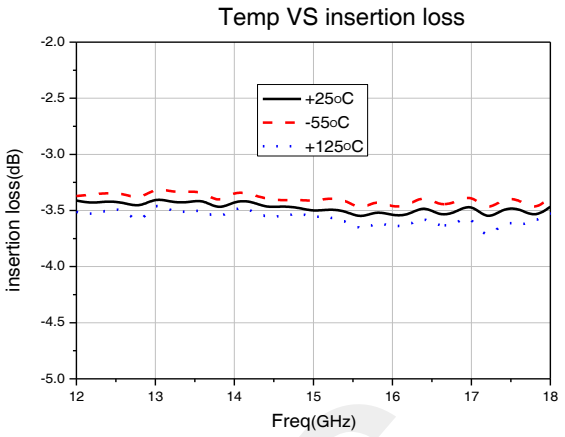
Description：

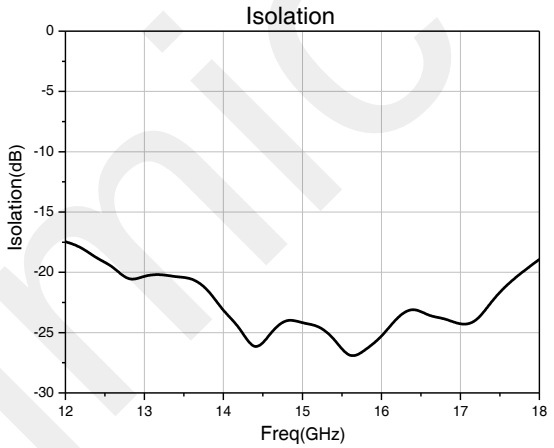
Unit: mm, tolerance: 0.05 mm Gold plating and grounding on the back of the chip Bonding press point gold plating, press point size: 0.10mm*0.10mm
Bonding cannot be performed on the through hole

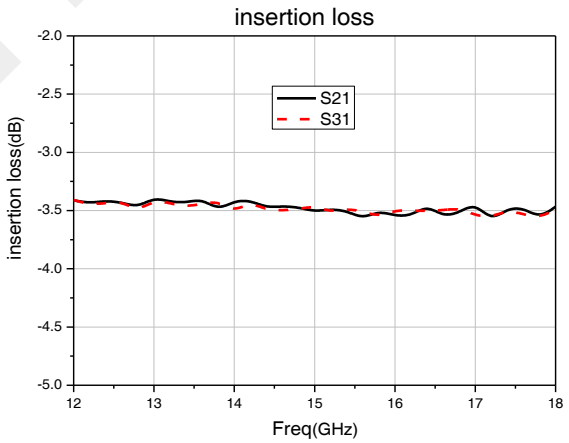
Pad description：

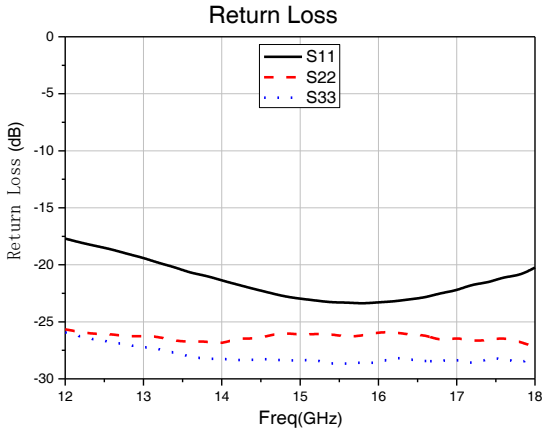
Pad number	Function	Fuction Description
1	RFin	RFInput，impedance) 50ohm
2、3	RFout	RF Output impedance 50ohm
	GND	

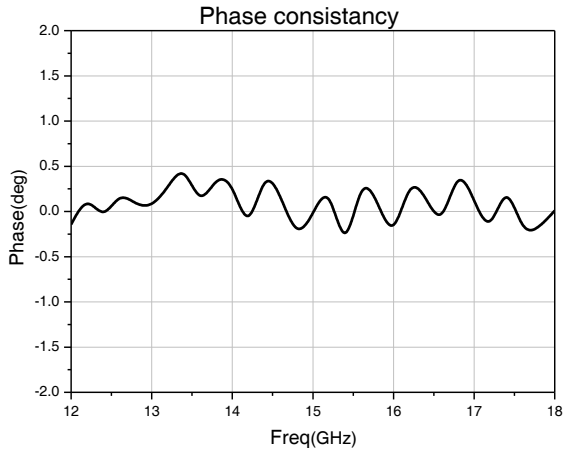
Typical curve：



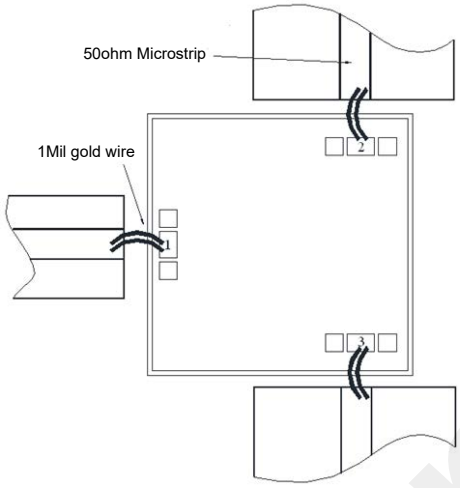








Assembly drawing：



The ceramic substrate should be as close to the chip as possible to shorten the size of the bond alloy wire.The typical assembly clearance is 0.076 - 0.152 mm (3 - 6 mils).

Instructions for assembly：

1. Storage: The chip must be placed in a container with electrostatic protection function and stored in a nitrogen atmosphere.
2. Cleaning: Bare chips must be operated and used in a clean environment. Cleaning the chips with liquid detergent is prohibited.
3. Electrostatic Protection: Please strictly observe ESD protection requirements to avoid electrostatic damage to the device.
4. General operation: Please use vacuum chuck or precision pointed tweezers to take the chip.Avoid touching the chip surface with tools or fingers during operation.
5. Mounting operation: AuSn solder eutectic sintering or conductive adhesive bonding can be used for chip mounting.The installation surface must be clean and level.
6. Bonding operation: ϕ 0.025 mm (1 mil) gold wire is used for both spherical and wedge bonding.
7. Therm oultrasonic bonding temperature is 150 C,Spherical bonding cleaver pressure 40 ~50gf, wedge bonding cleaver pressure 18 - 22gf.Use as little ultrasonic energy as possible. Bonding starts at the pressing point on the chip and ends at the package (or substrate)

Performance charactisitc：

- Freq Range：18～26GHz
- insertion loss：0.6dB
- input/ouput VSWR：1.4/1.1
- Chip size：1.5mm×4.0mm×0.1mm

General Description：

This product is a high performance GaAs MMIC 0° two-way splitter. The chip's Freq range covers 18-26GHz, the insertion loss is less than 0.6dB, and the input and output voltage VSWR is less than 1.4.

Electrical Spec：（TA=25℃）

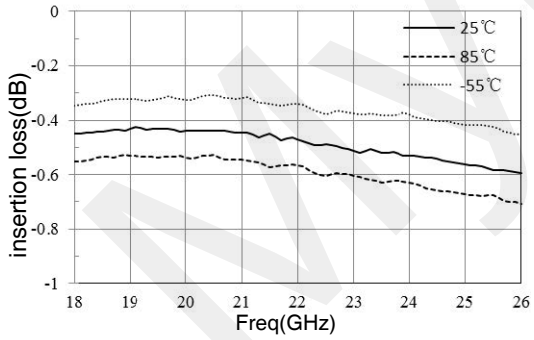
Item	Min	Typ	Max	Unit
Freq Range	18-26			GHz
Insertion loss	0.4		0.6	dB
Insl Fluctuation			±0.1	dB
Isolation	18			dB
Input VSWR			1.4	-
Output VSWR			1.1	-

Absolute Max. Ratings：

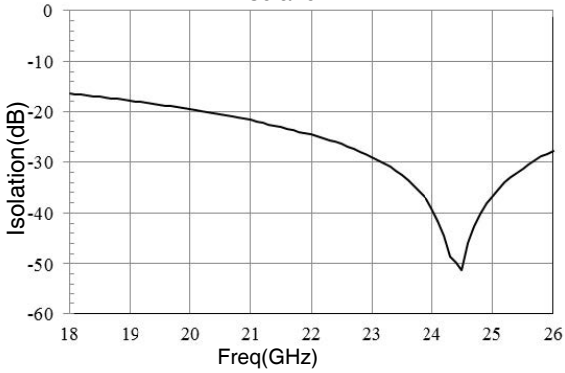
Max input Power	+37dBm
Storage temp	-65℃-150℃
Operation Temp	-55℃-125℃

Typical curve：

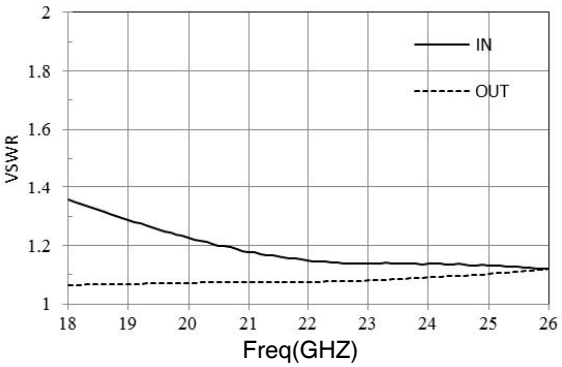
insertion loss



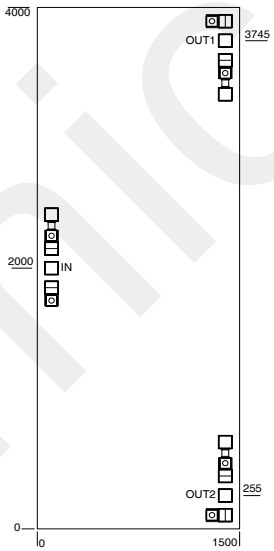
Isolation



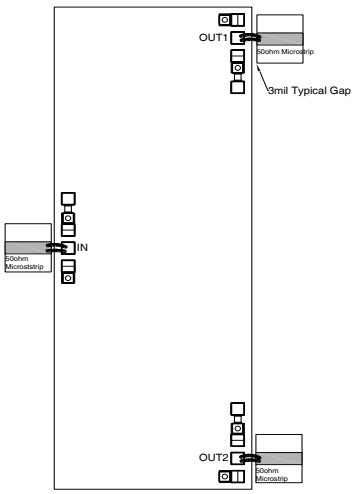
VSWR



Outline drawing：（Unitμm）



Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output with 2 (25um diameter gold wire) bonding wires, the bonding wire length is as short as possible;
- The input and output have a DC blocking capacitor.
- This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage

Performance charactisitc：

- Freq Range：18～26GHz
- insertion loss：0.7dB
- Insertion loss fluctuation：±0.2dB
- Isolation：22dB
- input/ouput VSWR：1.2/1.4
- Chip size：1.35mm×1.8mm×0.075mm

General Description：

This product is a GaAs MMIC0° two-way power splitter chip. The power splitter chip has the characteristics of small insertion loss, high Isolation, small size and easy integration. It is widely used in power distribution and synthesis. Its Freq Range covers 18 to 26 GHz, and the insertion loss in the entire Freq range is less than 0.9 dB.

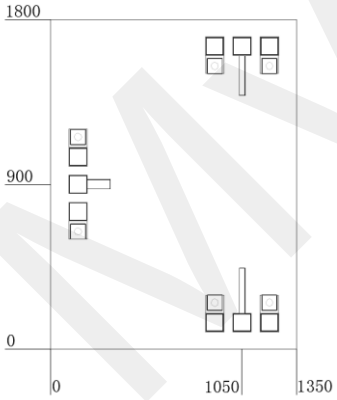
Electrical Spec：（TA=25℃，VD=+5V)

Item	Min	Typ	Max	Unit
Freq Range		18-26		GHz
insertion loss	0.5	0.7	0.9	dB
Insl Fluctuation			±0.2	dB
Isolation	22			dB
Input VSWR		1.2		-
Output VSWR		1.4		-

Absolute Max. Ratings：

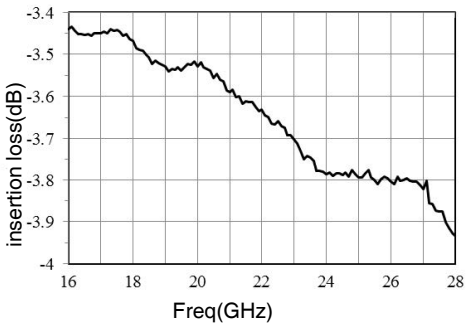
Max input Power	+37dBm
Storage temp	-65℃-+150℃
Operation Temp	-55℃-+125℃

Outline drawing：（Unitμm）

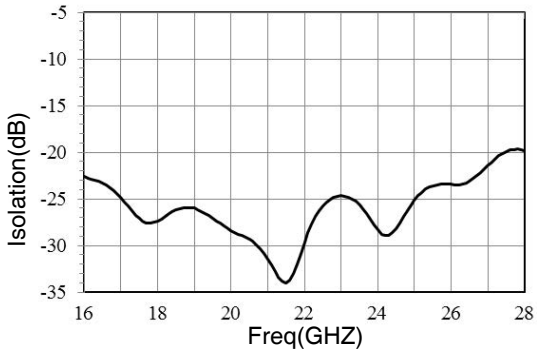


Typical curve：

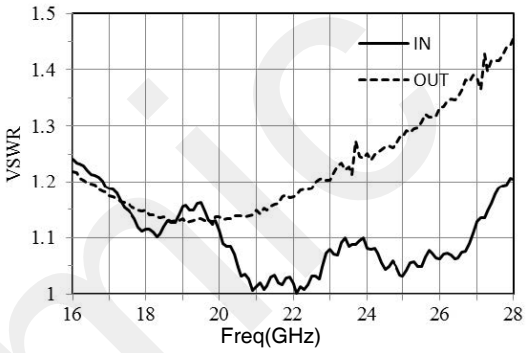
insertion loss



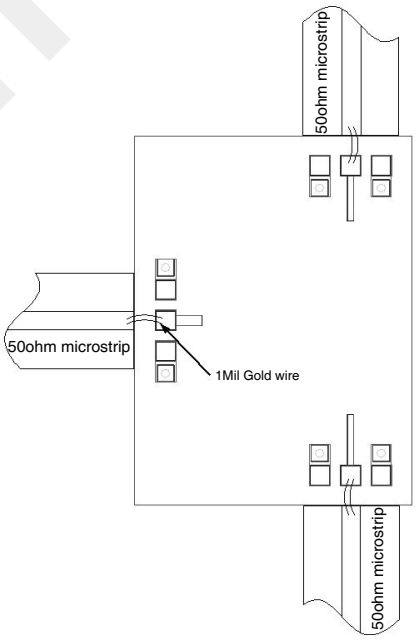
Isolation



VSWR



Assembly drawing：



Notes：

- When used in a clean environment, do not touch the surface of the chip.
- Input and output with 2 (25um diameter gold wire) bonding wires, the bonding wire length is as short as possible;
- The input and output have a DC blocking capacitor.
- This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.
- Dry, nitrogen environment storage

Performance charactisitc：

- Freq Range：12～26.5 GHz
- Insertion Loss：0.7 dB
- Isolation：20dB
- return loss：＞16dB/＞15dB
- Chip size：1.5mm×2.0mm×0.1mm
- interface：50Ω Coplanar wave-guide line

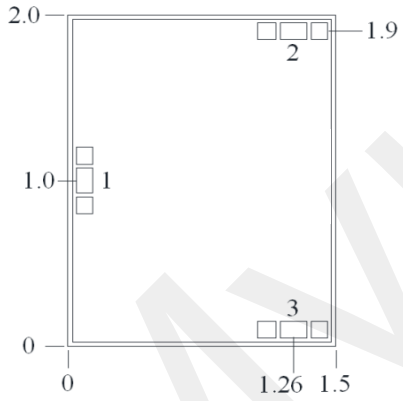
General Description

This product is a gallium arsenide monolithic power divider chip.The power splitter chip has the characteristics of small insertion loss, high Isolation, small volume, light weight, easy integration, and the like, and is widely used in power distribution and synthesis.The chip uses an on-chip via metallization process to ensure good grounding.The back side is metallized for eutectic sintering and conductive bonding.

Absolute Max. Ratings：

Max Input Power	+30dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃～+125℃

Outline drawing：（Unitmm）



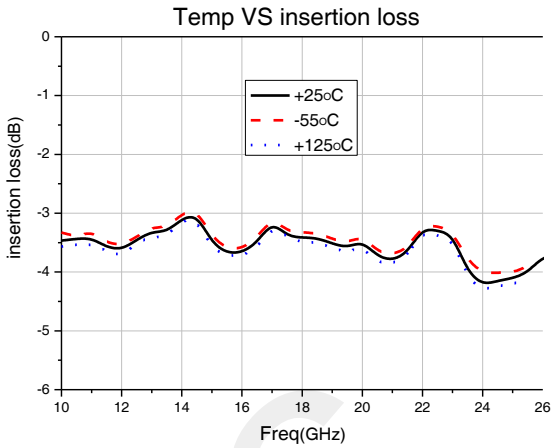
Description：

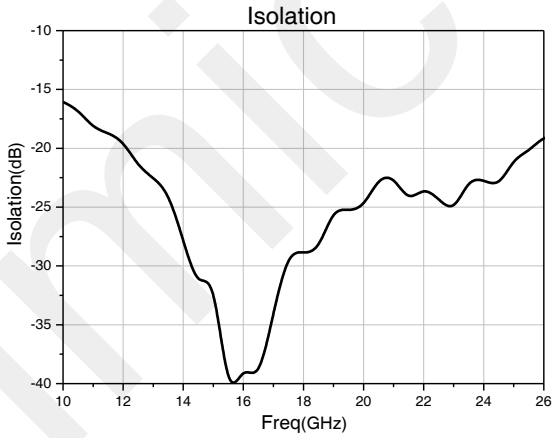
Unit: mm, tolerance: 0.05 mm
Gold plating and grounding on the back of the chip Bonding press point gold plating, press point size:
0.10mm*0.10mm
Bonding cannot be performed on the through hole

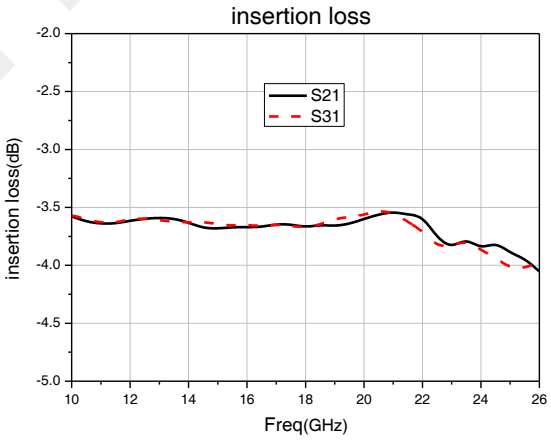
Pad description：

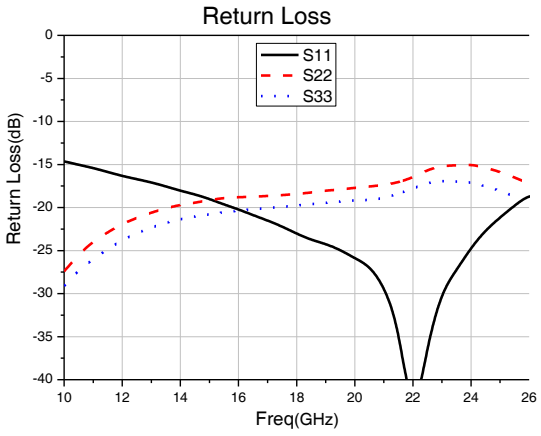
Pad number	Function	Fuction Description
1	RFin	RFInput，impedance) 50ohm
2、3	RFout	RF Output impedance 50ohm
	GND	

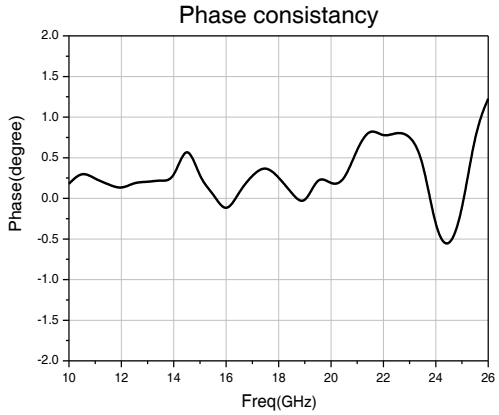
Typical curve：



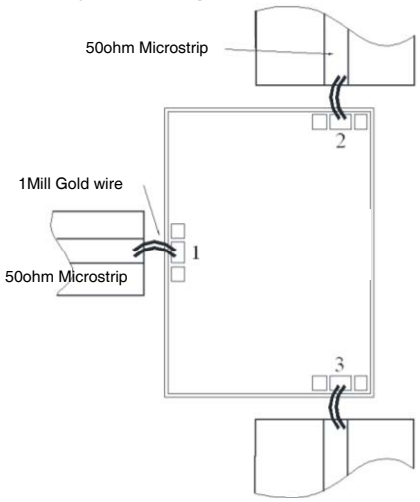








Assembly drawing：



The ceramic substrate should be as close to the chip as possible to shorten the size of the bond alloy wire.The typical assembly clearance is 0.076 - 0.152 mm (3 - 6 mils).

Notes：

1. Storage: The chip must be placed in a container with electrostatic protection function and stored in a nitrogen atmosphere.
2. Cleaning: Bare chips must be operated and used in a clean environment. Cleaning the chips with liquid detergent is prohibited.
3. Electrostatic Protection: Please strictly observe ESD protection requirements to avoid electrostatic damage to the device.
4. General operation: Please use vacuum chuck or precision pointed tweezers to take the chip.Avoid touching the chip surface with tools or fingers during operation.
5. Mounting operation: AuSn solder eutectic sintering or conductive adhesive bonding can be used for chip mounting.the installation surface must be clean and level.
6. Bonding operation: Φ 0.025 mm (1 mil) gold wire is used for both spherical and wedge bonding.
7. Thermoultrasonic bonding temperature is 150 C,Spherical bonding cleaver pressure 40 ~50gf, wedge bonding cleaver pressure 18 - 22gf.Use as little ultrasonic energy as possible. Bonding starts at the pressing point on the chip and ends at the package (or substrate)

Performance charactisitc：

- Freq Range：20～40 GHz
- Insertion Loss：0.7 dB
- Isolation：20dB
- Input/Output VSWR：1.5/1.3
- Chip size：1.65mm×1.2mm×0.1mm
- interface：50Ω Coplanar waveguide line

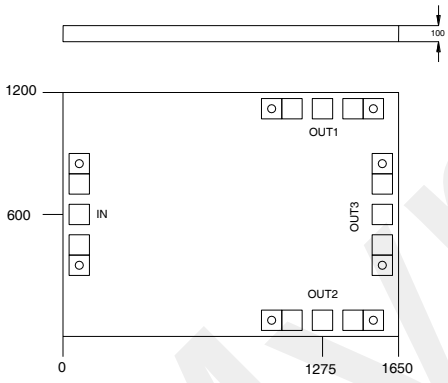
General Description：

This product is a GaAS single-chip 0° three-power splitter chip.The power splitter chip has the characteristics of small insertion loss, high Isolation, small volume, light weight and easy integration, and is widely used in power distribution and synthesis. the chip uses an on-chip via metallization process to ensure good grounding..The back side is metallized for eutectic sintering or conductive bonding.

Absolute Max. Ratings：

Max Input Power	+15dBm
Storage temp	-65℃～+150℃
Operation Temp	-55℃ ～+125℃

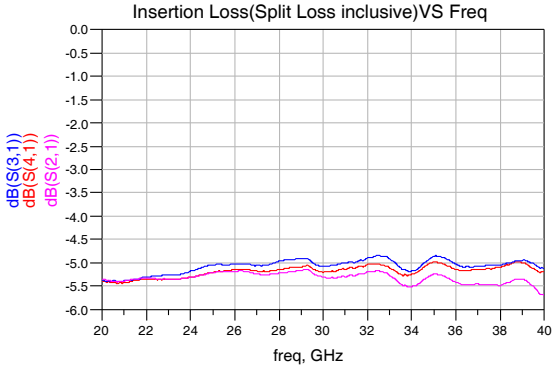
Outline drawing：（Unitum）

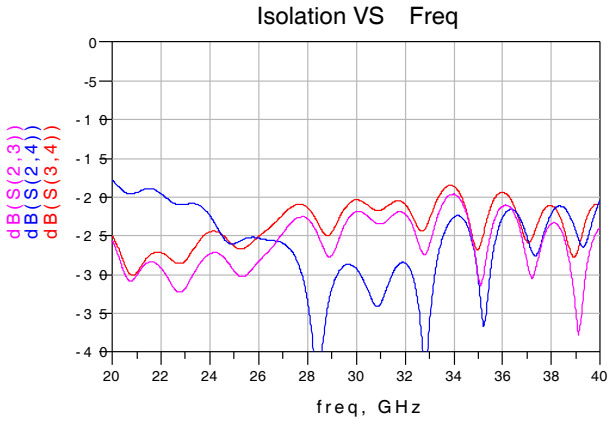


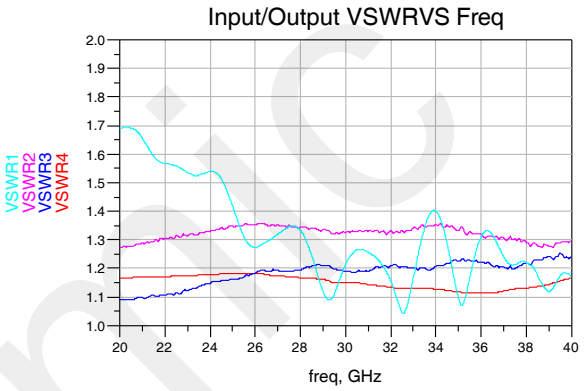
Description：

Unit: mm, tolerance: 0.05 mm
Gold plating and grounding on the back of the chip Bonding press point gold plating, press point size:
0.10mm*0.10mm
Bonding cannot be performed on the through hole

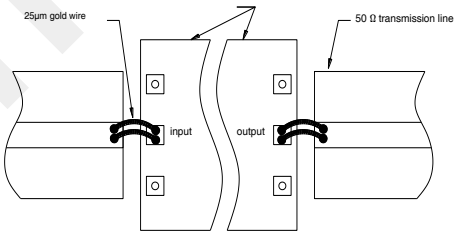
Typical curve：







Assembly drawing：



The ceramic substrate should be as close to the chip as possible to shorten the size of the bond alloy wire.The typical assembly clearance is 0.076 - 0.152 mm (3 - 6 mils).

Instructions for assembly：

1. Storage: The chip must be placed in a container with electrostatic protection and stored under nitrogen.

2. Cleaning treatment: The bare chip must be used in a clean environment. It is forbidden to clean the chip with liquid detergent.

3. Electrostatic protection: Please strictly comply with ESD protection requirements to avoid electrostatic damage to the device.

4. Routine operation: Use a vacuum chuck or a precision pointed tweezers to take the chip.avoid touching tools or fingers on the surface of the chip during operation.

5. Mounting operation: The chip can be mounted by AuSn solder eutectic sintering or conductive bonding.the mounting surface must be clean and flat.

6. Bonding operation: Φ 0.025mm (1mil) gold wire is used for spherical or wedge bonding.The thermosonic bonding temperature was 150 °C.
The spherical bonding boring tool pressure is 40 to 50 gf, and the wedge-shaped bonding boring tool pressure is 18 to 22 gf. Use as little ultrasonic energy as possible. The bonding starts at the pressure point on the chip and ends at the package (or substrate).

Performance charactisitc：

- Freq Range：18～40GHz
- insertion loss：0.6dB
- input/ouput VSWR：1.4/1.4
- Chip size：1.5mm×3.2mm×0.1mm

General Description：

This product is a high performance GaAs MMIC 0° two-way splitter. The chip's Freq range covers 18-40GHz, the insertion loss is less than 0.6dB, and the input and output voltage VSWR is less than 1.4.

Electrical Spec：（T_A=25℃）

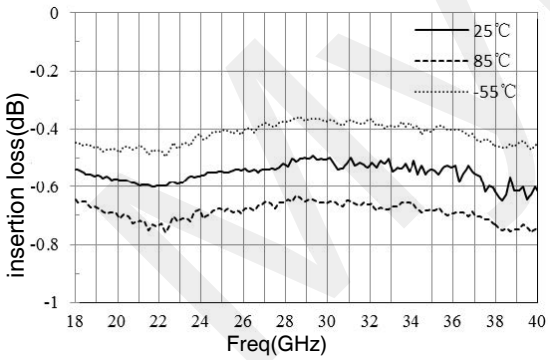
Item	Min	Typ	Max	Unit
Freq Range	18-40			GHz
Insertion loss	0.5		0.6	dB
Insl Fluctuation			±0.1	dB
Isolation	11			dB
Input VSWR			1.4	-
Output VSWR			1.4	-

Absolute Max. Ratings：

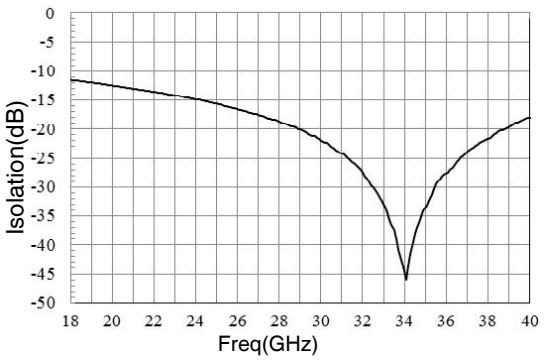
Max input Power	+37dBm
Storage temp	-65℃-+150℃
Operation Temp	-55℃-+125℃

Typical curve：

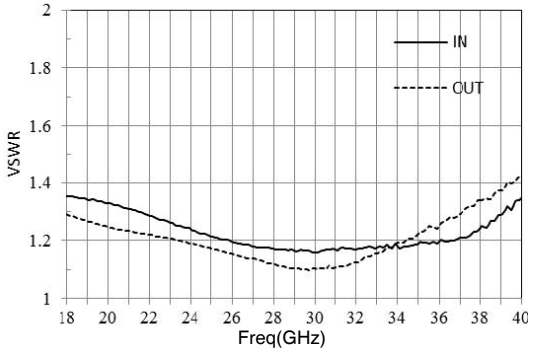
insertion loss



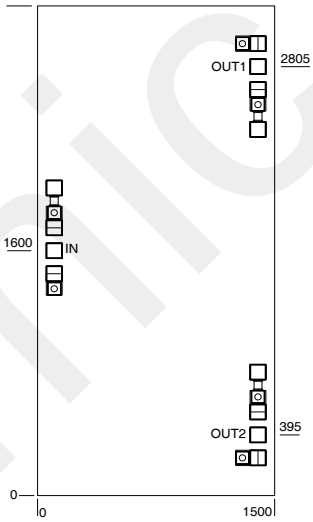
Isolation



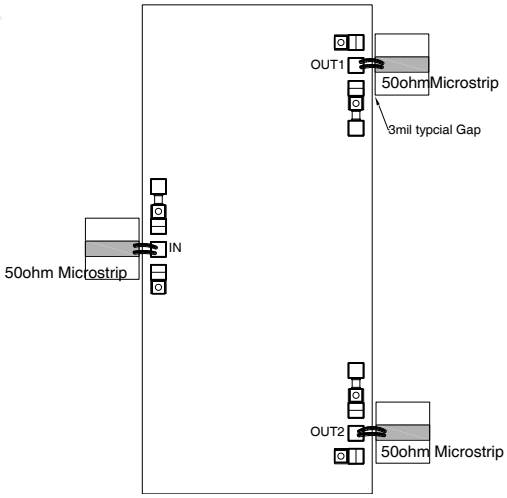
VSWR



Outline drawing：（Unitμm）



Assembly drawing：



Notes：

•When used in a clean environment, do not touch the surface of the chip.
•Input and output are made of two (25um diameter gold wire) bonding wires, with a bonding wire length of about 300 um being optimal.
•This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.no need DC-Blocking capacitor in input/output
•Dry, nitrogen environment storage.

Performance charactisitc：

- Freq Range：18～40GHz
- insertion loss：0.8dB
- Insertion loss fluctuation：±0.2dB
- Isolation：25dB
- input/ouput VSWR：1.2/1.1
- Chip size：1.5mm×1.5mm×0.075mm

General Description：

This product is a GaAs MMIC0° two-way power splitter chip. The power splitter chip has the characteristics of small insertion loss, high Isolation, small size, light weight and easy integration. Its Freq Range covers 18~40GHz.

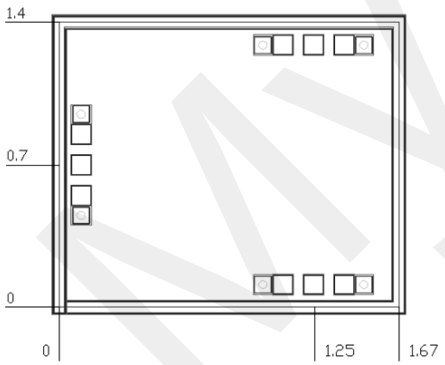
Electrical Spec：（T_A=25℃，VD=+5V)

Item	Min	Typ	Max	Unit
Freq Range	18-40			GHz
insertion loss	0.6	0.8	1.0	dB
Insl Fluctuation			±0.2	dB
Isolation	22	25		dB
Input VSWR		1.2	1.4	-
Output VSWR		1.1	1.3	-

Absolute Max. Ratings：

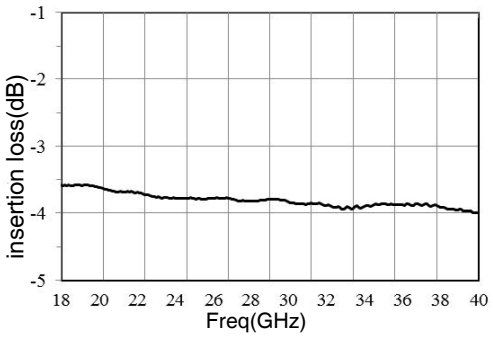
Max input Power	+37dBm
Storage temp	-65℃-+150℃
Operation Temp	-55℃-+125℃

Outline drawing：（Unitmm）

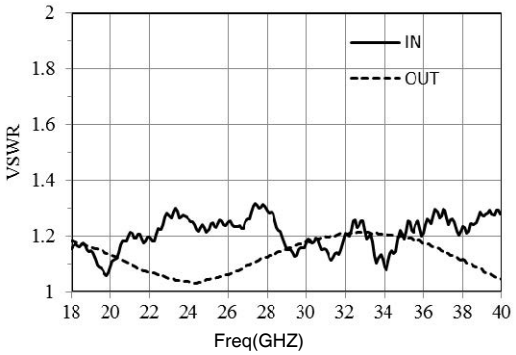


Typical curve：

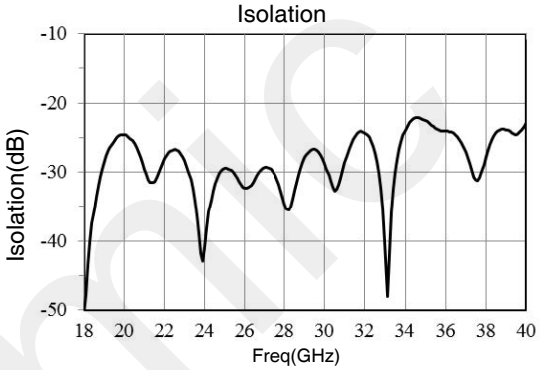
insertion loss



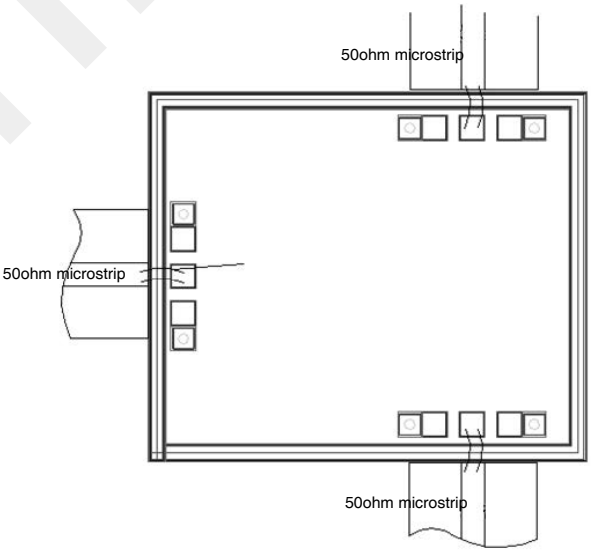
Input/Output VSWR



Isolation



Assembly drawing：



Notes：

•When used in a clean environment, do not touch the surface of the chip.
•Input and output are made of two (25um diameter gold wire) bonding wires, with a bonding wire length of about 300 um being optimal.
•This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.no need DC-Blocking capacitor in input/output
•Dry, nitrogen environment storage.

Performance charactisitc：

- Freq range： 26～31GHz
- insertion loss：0.7dB
- Insertion loss fluctuation：±0.2dB
- Isolation：24dB
- input/ouput VSWR：1.3/1.2
- Chip size：1.25mm×1.8mm×0.075mm

General Description：

This product is a GaAs MMIC0° two-way power splitter chip. The power splitter chip has the characteristics of small insertion loss, high Isolation, small size and easy integration. It is widely used in power distribution and synthesis. Its Freq Range covers 26 to 31 GHz, and the insertion loss in the entire Freq range is less than 0.7 dB.

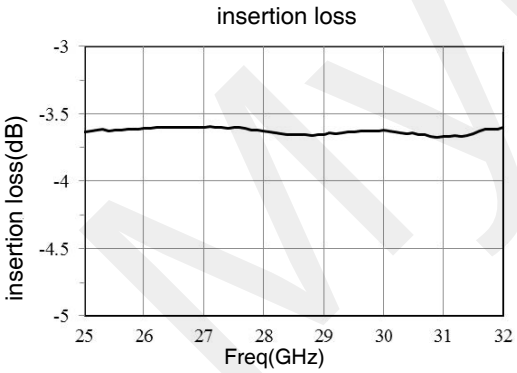
Electrical Spec：（T_A=25℃，VD=+5V）

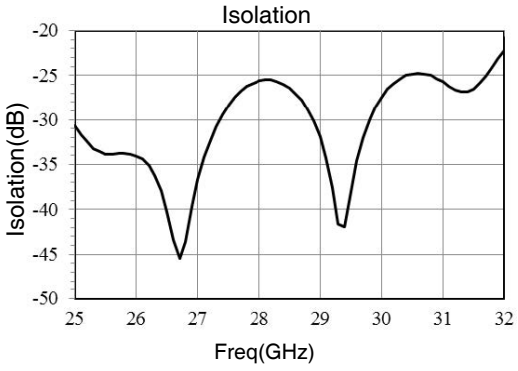
Item	Min	Typ	Max	Unit
Freq Range	26-31			GHz
Insertion loss	0.5	0.7	0.9	dB
Insl fluctuation			±0.2	dB
Isolation	24			dB
Input VSWR		1.3		-
Output VSWR		1.2		-

Absolute Max. Ratings：

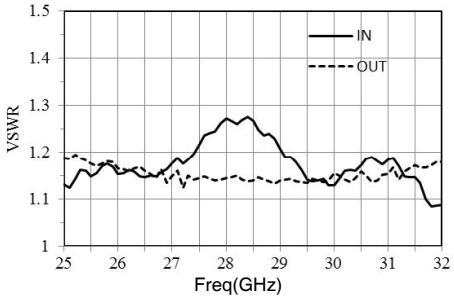
Max Input Power	+37dBm
Storage temp	-65℃~150℃
Operation Temp	-55℃~125℃

Typical curve：

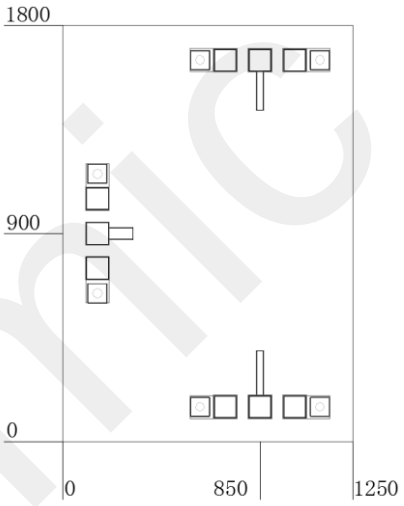




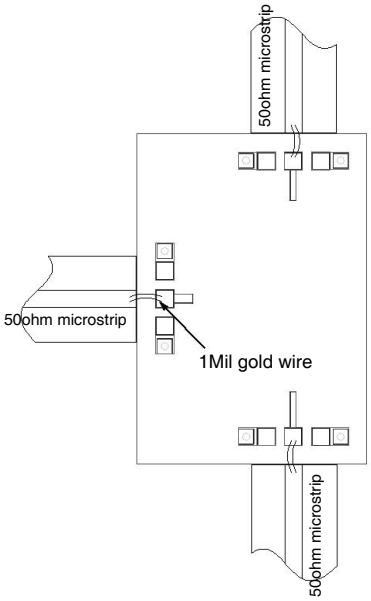
VSWR



Outline drawing：(Unit μm)



Assembly drawing：



Notes：

•When used in a clean environment, do not touch the surface of the chip.
•Input and output are made of two (25um diameter gold wire) bonding wires, with a bonding wire length of about 300 um being optimal.
•This product is an electrostatic sensitive device. Pay attention to anti-static when storing and using it.no need DC-Blocking capacitor in input/output
•Dry, nitrogen environment storage.

Performance charactisitc：

- Freq Range：26～40GHz
- insertion loss：0.5dB
- input/ouput VSWR：1.4/1.1
- Chip size：1.5mm×3.2mm×0.1mm

General Description：

This product is a high performance GaAs MMIC 0° two-way splitter.The chip Freq range covers 26-40GHz, the insertion loss is less than 0.5dB, and the input and output voltage VSWR is less than 1.4.

Electrical Spec：（TA=25℃）

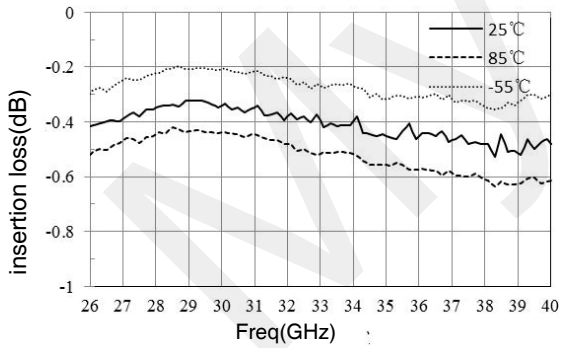
Item	Min	Typ	Max	Unit
Freq Range	26-40			GHz
Insertion loss	0 .3		0.5	dB
NSL Fluctuation			±0.1	dB
Isolation	13			dB
Input VSWR			1.4	-
Output VSWR			1.1	-

Absolute Max. Ratings：

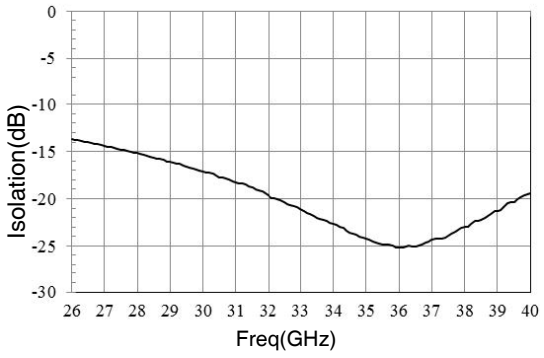
Max input Power	+37dBm
Storage temp	-65℃-150℃
Operation Temp	-55℃-125℃

Typical curve：

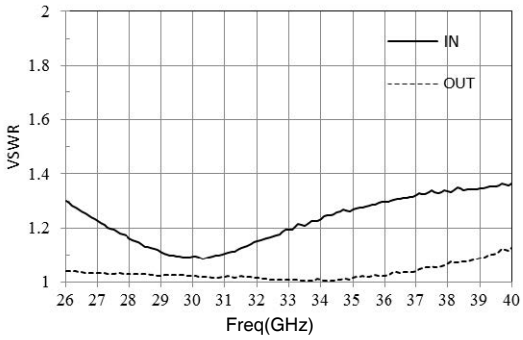
insertion loss



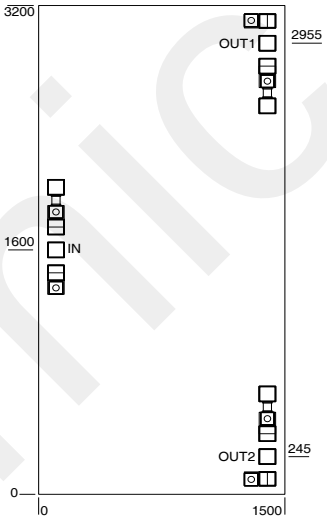
Isolation



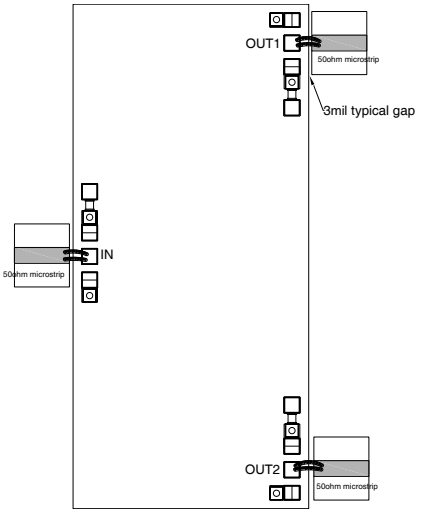
VSWR



Outline drawing：（Unitμm）



Assembly drawing：



Notes：

•When used in a clean environment, do not touch the surface of the chip.
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•Dry, nitrogen environment storage.